

Pixel chip testing at DESY

Daniel Pitzl, Alexey Petrukhin DESY
Meeting at PSI, 24/01/2012

- Installation at DESY
- Some test results
- Known issues, open questions

Universal pixel test board

Design and firmware
by Beat Meier, PSI

600 V
bias

psi46
chip

other
adapters
available

scope

ADC

trigger

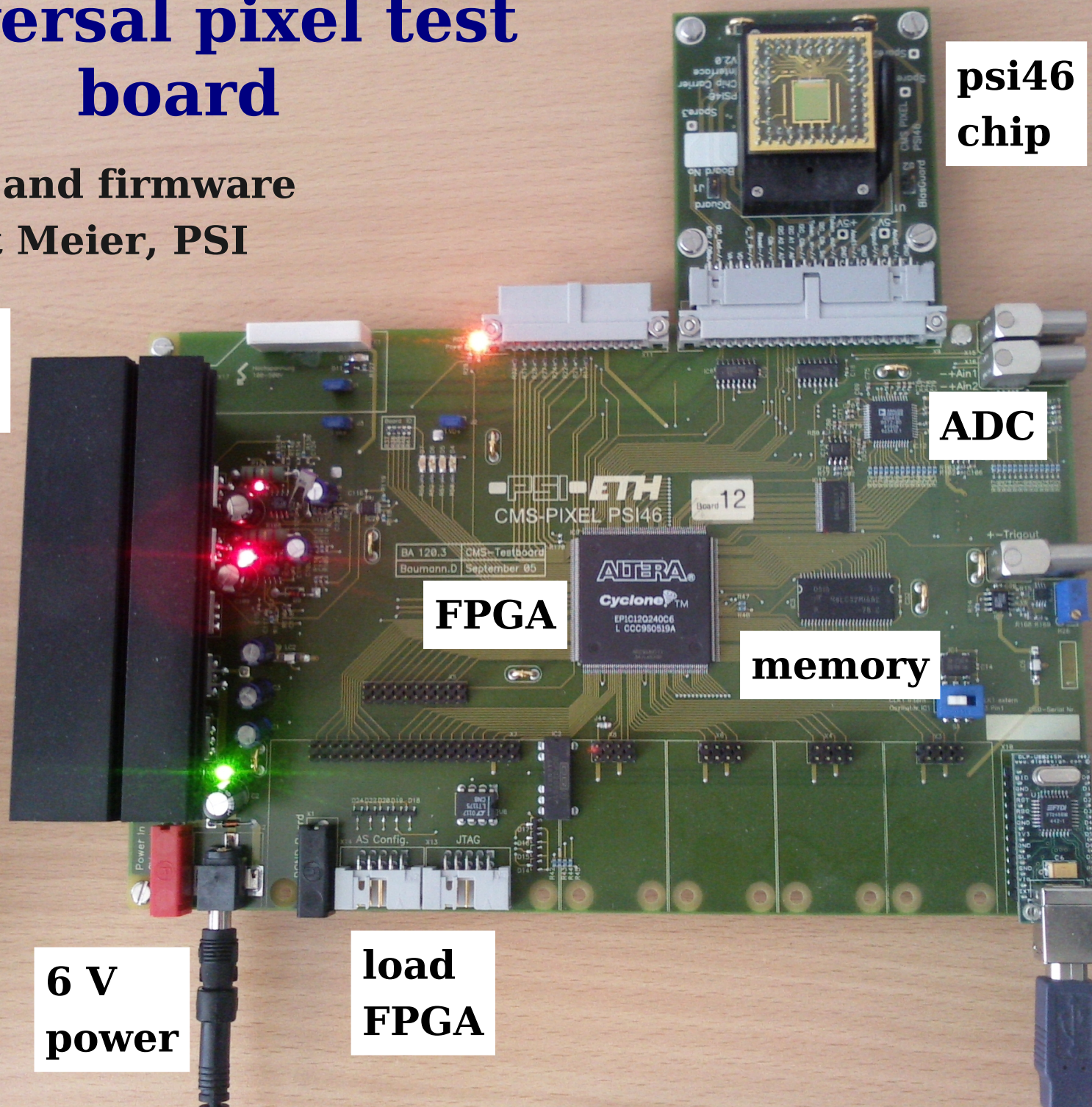
FPGA

memory

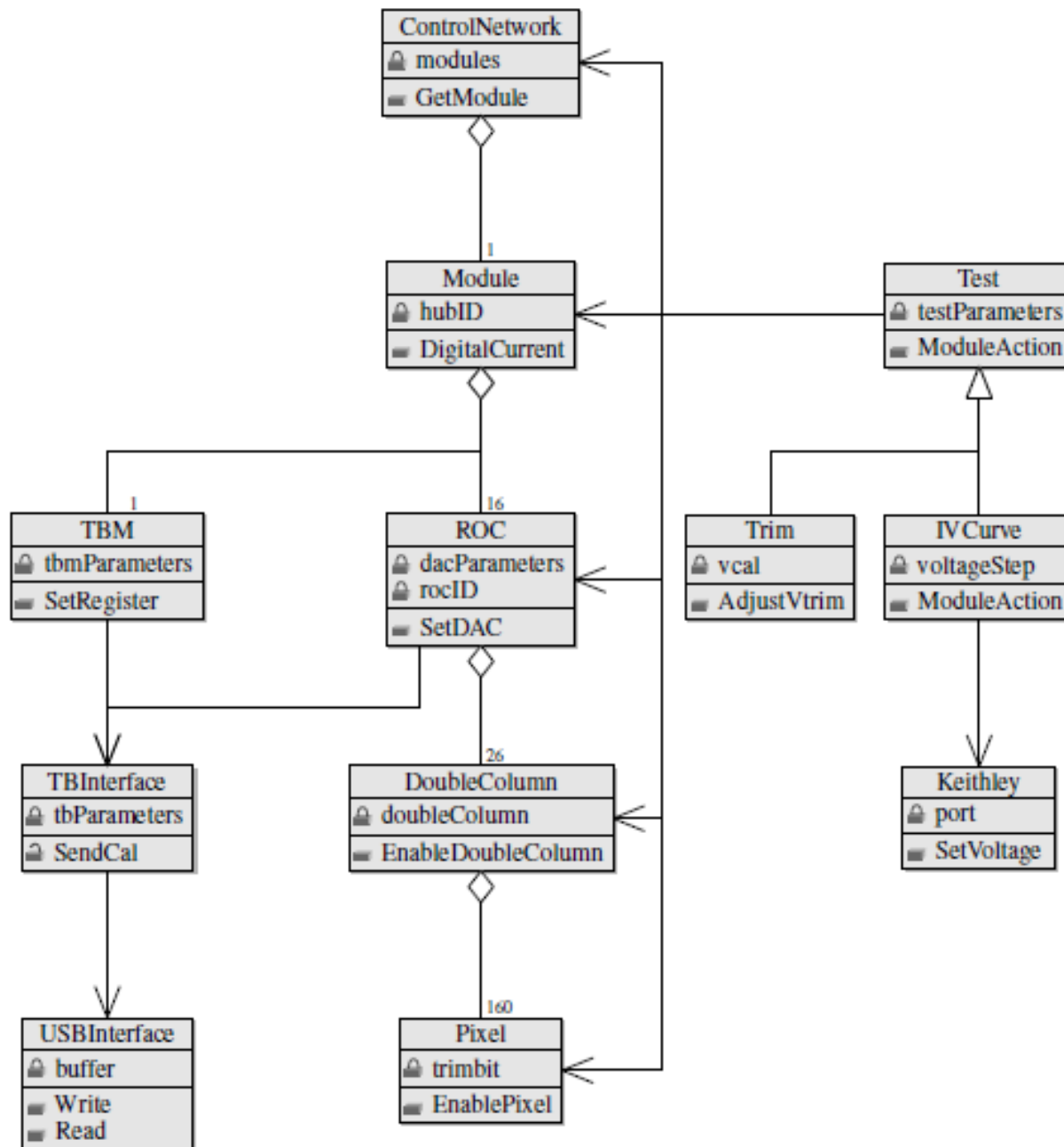
USB1
to
laptop

6 V
power

load
FPGA



psi46expert software



- C++ class library.
- Written by Peter Trüb (ETH, 2005-2007) for Scientific Linux 32 bit.
- Now compiled with g++ 4.4.5 under Ubuntu 10.10 and SL6 64 bit.
- USB interface required some changes (long → int).

Configuration

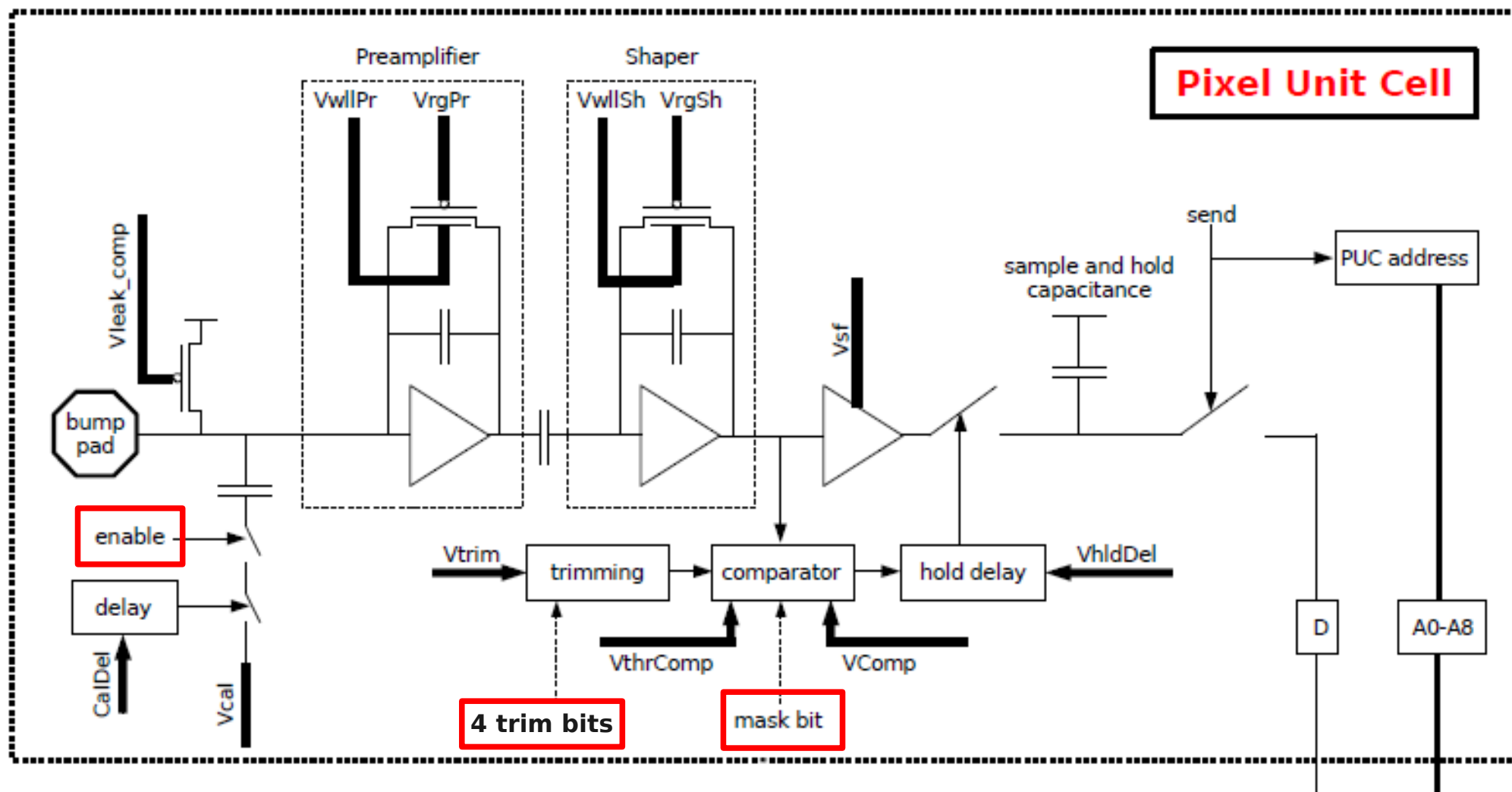
- Configuration files for test board and readout chip imported from PSI:
 - board name,
 - run in 40 MHz mode,
 - set 26 DACs and Control Registers on the ROC,
 - define timing sequence: reset - cal - trigger - token,
 - read and load calibration and trim values,
 - run in 'psi46expert' or 'takeData' mode

psi46 DACs

1	Vdig	6
2	Vana	150
3	Vsf	160
4	Vcomp	10
5	Vleak_comp	0
6	VrgPr	0
7	VwllPr	35
8	VrgSh	0
9	VwllSh	35
10	VhldDel	130
11	Vtrim	7
12	VthrComp	124
253	CtrlReg	0
254	WBC	20

13	VIBias_Bus	30
14	Vbias_sf	10
15	Voffset0p	55
16	VIbias0p	115
17	VOffsetR0	120
18	VIon	115
19	VIbias_PH	130
20	Ibias_DAC	122
21	VIbias_roc	220
22	VIColOr	100
23	Vnpix	0
24	VSumCol	0
25	Vcal	200
26	CalDel	125
27	RangeTemp	0

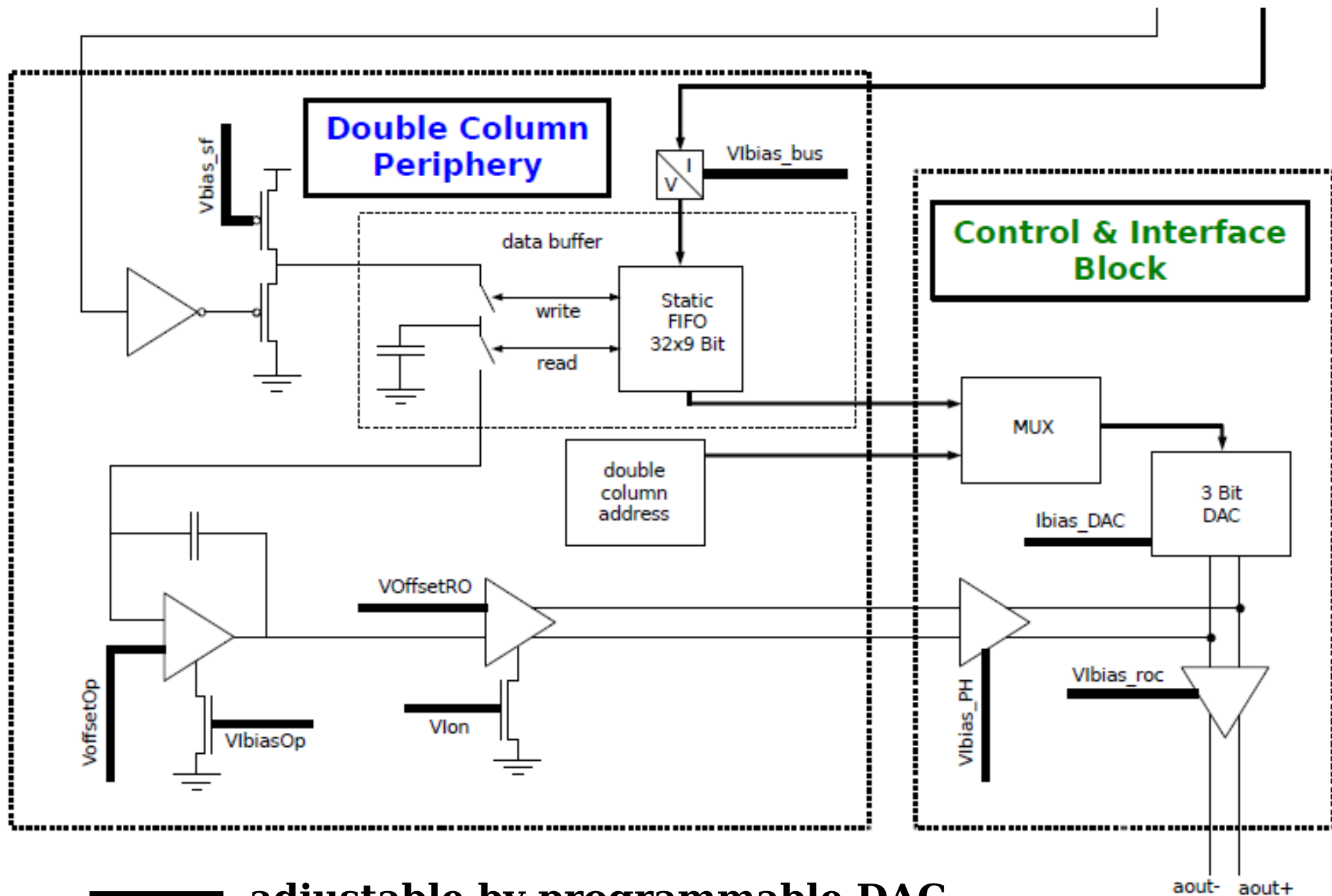
psi46 pixel readout chip



— adjustable by programmable DAC, per ROC

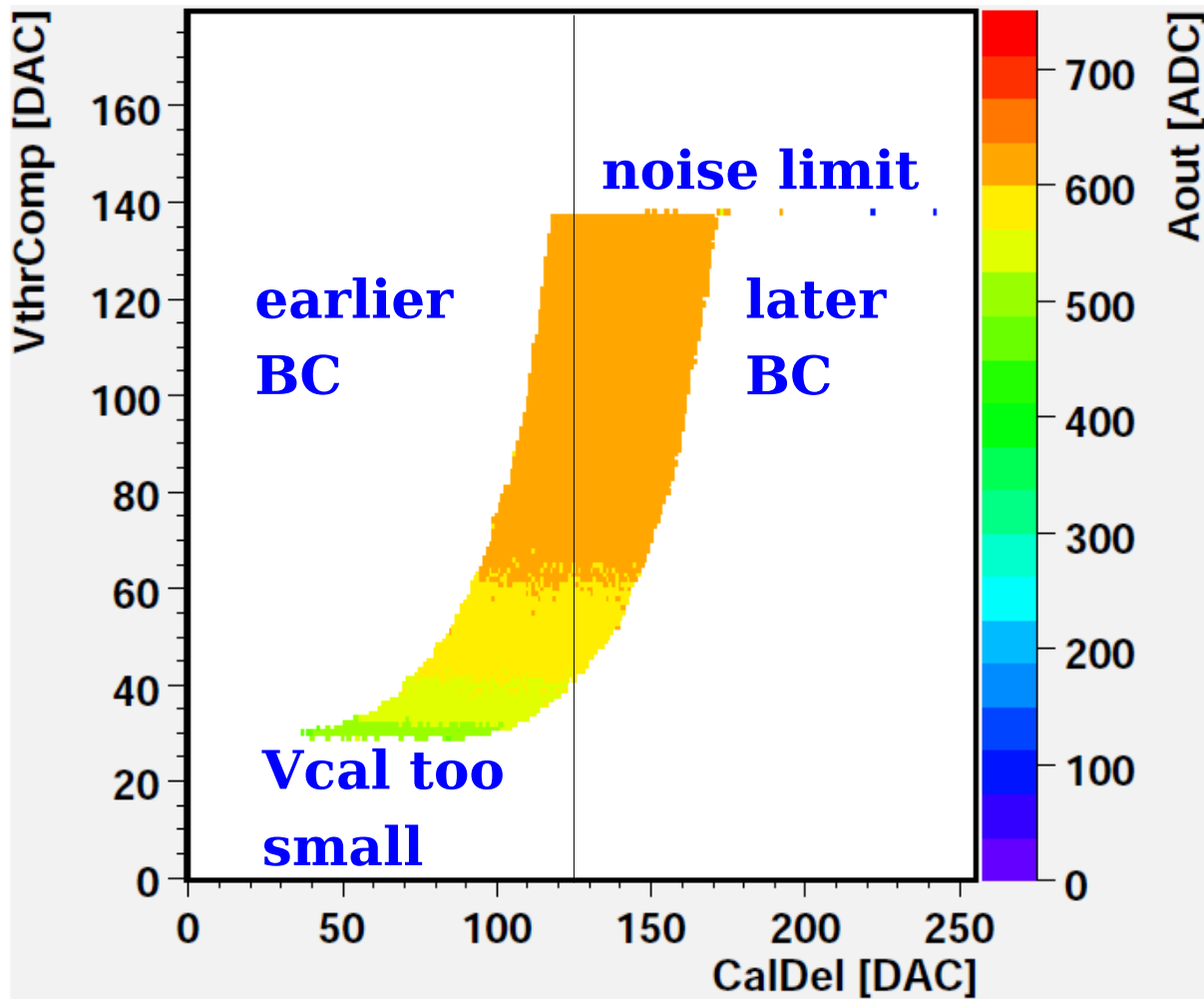
□ programmable register, per pixel

psi46 pixel readout chip

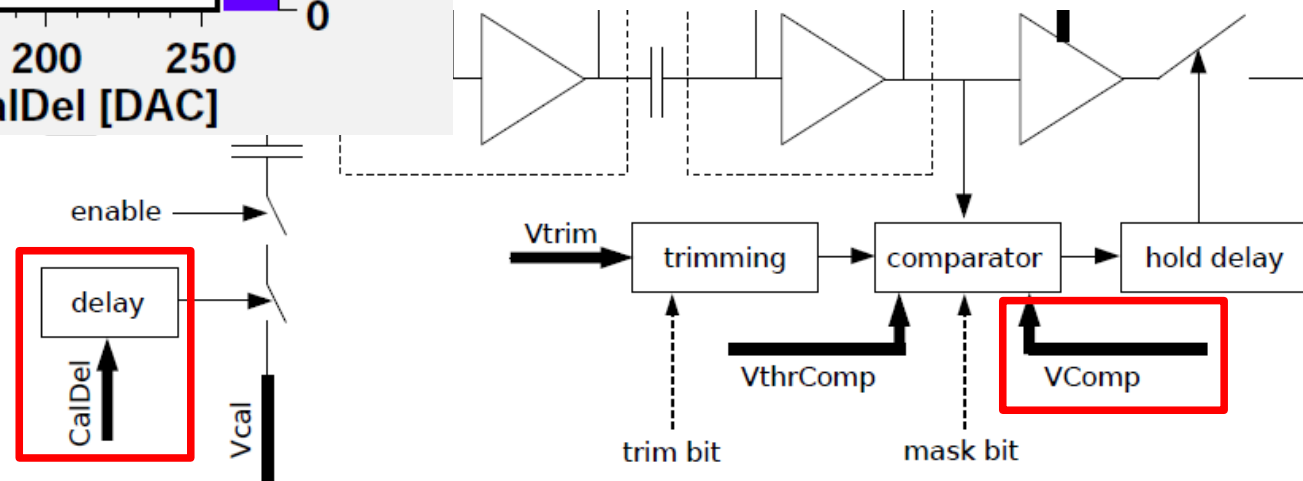


Some test results

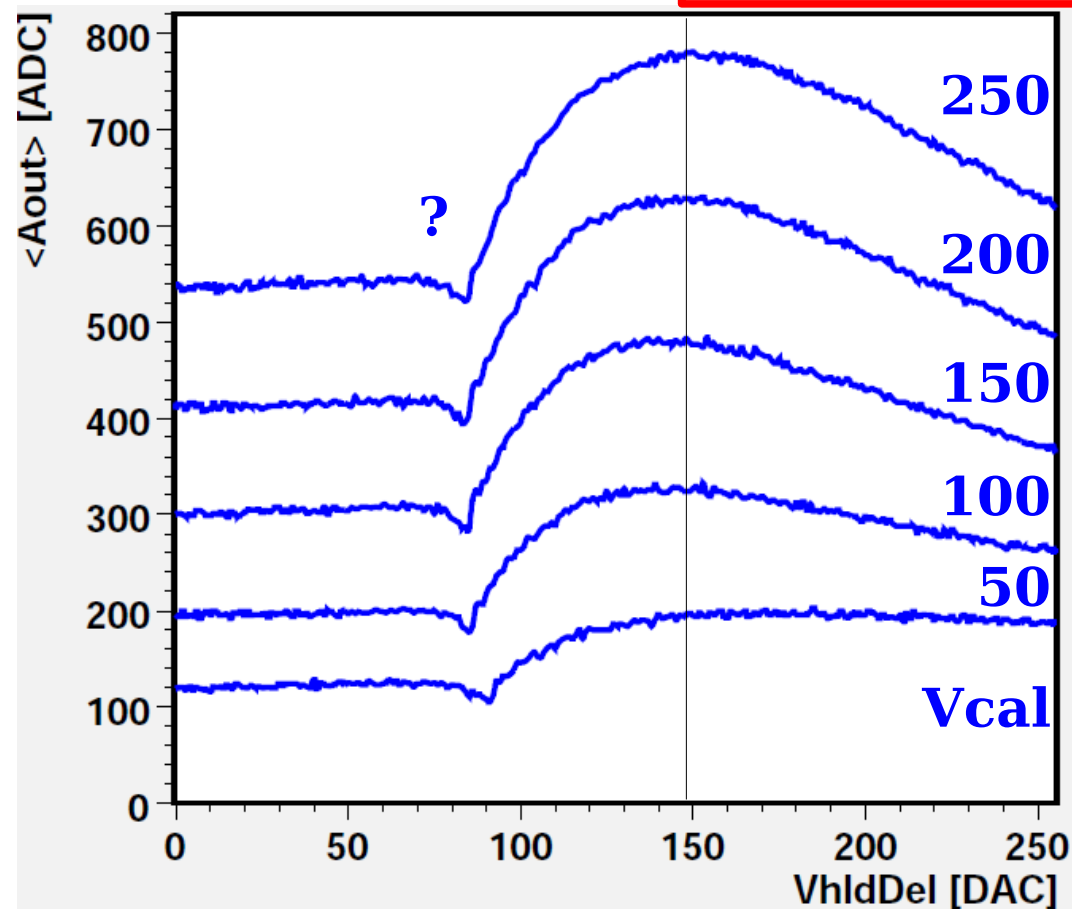
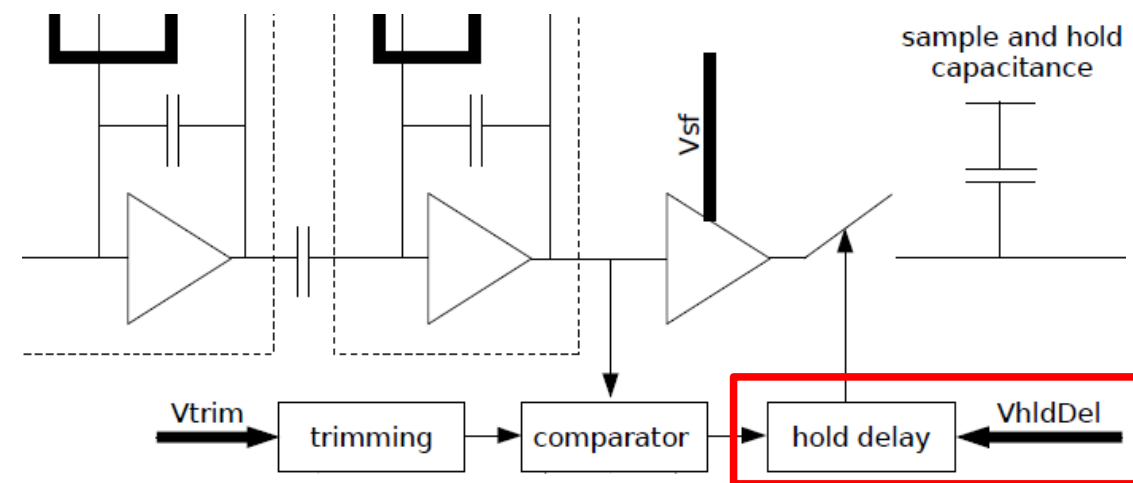
CalDel and Time walk



- One pixel.
- Vcal 200 small DAC.
- Moving the threshold shifts the timing:
 - time walk.

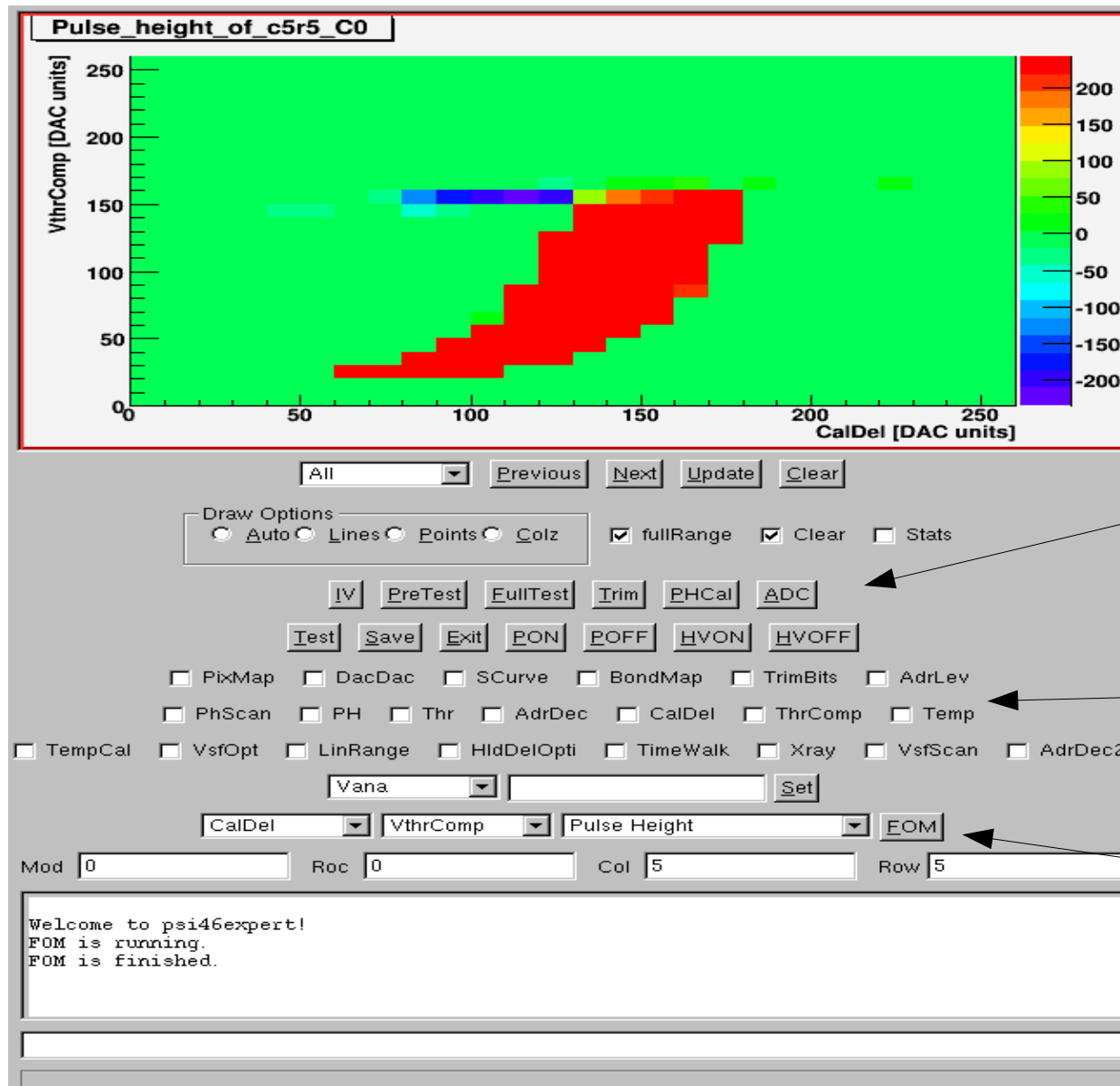


Sample and hold timing



- One pixel.
- Position of maximum depends on pulse height:
‣ time walk.
- DAC 150 is compromise

GUI



Calibration tests

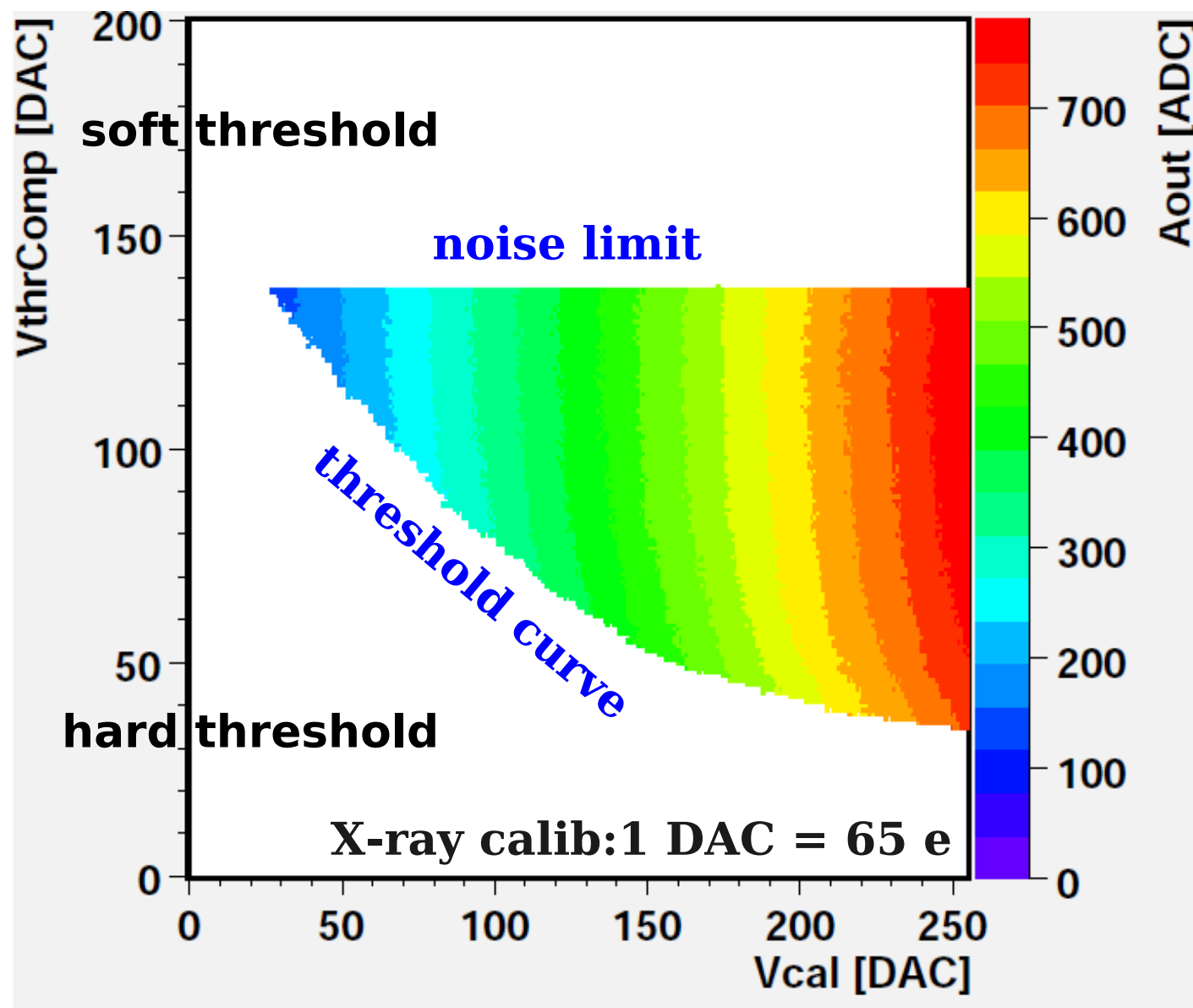
Individual tests

Parameter adjusting

Threshold optimization algorithm

- If comparator thresholds are adjusted with global VthrComp only: spread of thresholds in ROC ~ 300 e⁻ due to transistor mismatches
- Unify pixel thresholds by 4 trim bits (values from 0 to 15) and scale with Vtrim DAC
- Each trim bit value is set such that Vcal -threshold of the pixel differs least from the selected target threshold in the procedure
- threshold spread reduced to 50(80) e⁻ after the optimization chip without(with) sensor

Comparator threshold

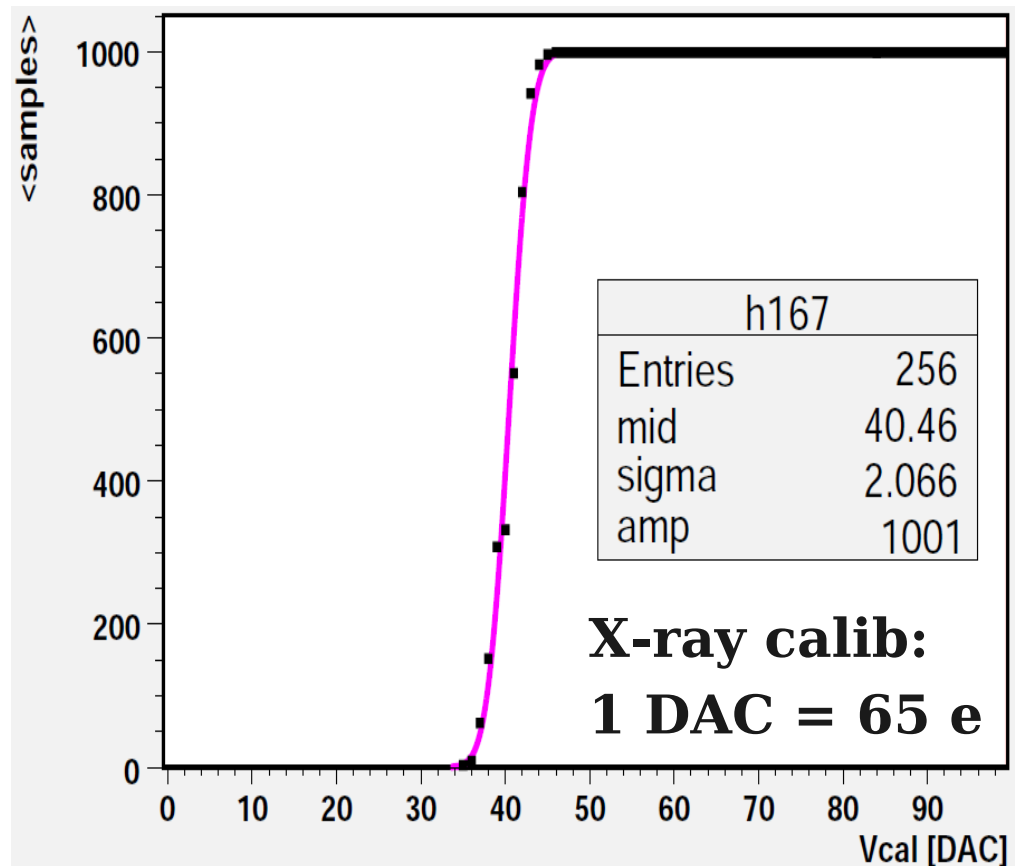


- One pixel
- Analog pulse height vs threshold and calibrate amplitude.
- White region:
 - no signal.
- Colored bands are not vertical:
 - time walk.

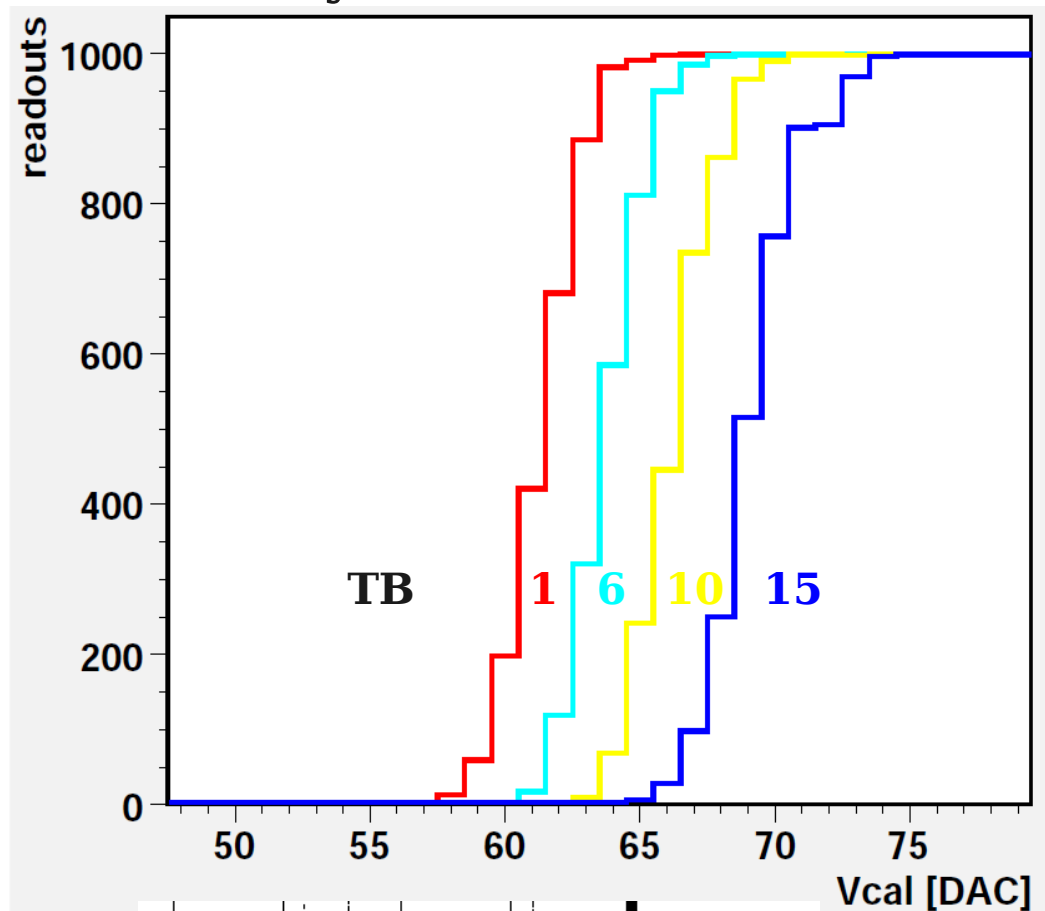
Threshold curve

one pixel

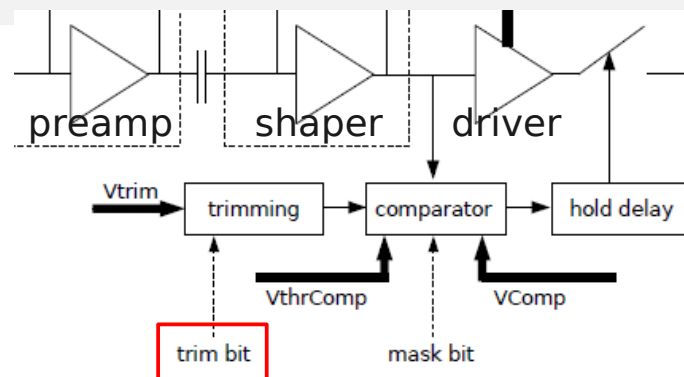
vary test pulse amplitude



vary trim bits

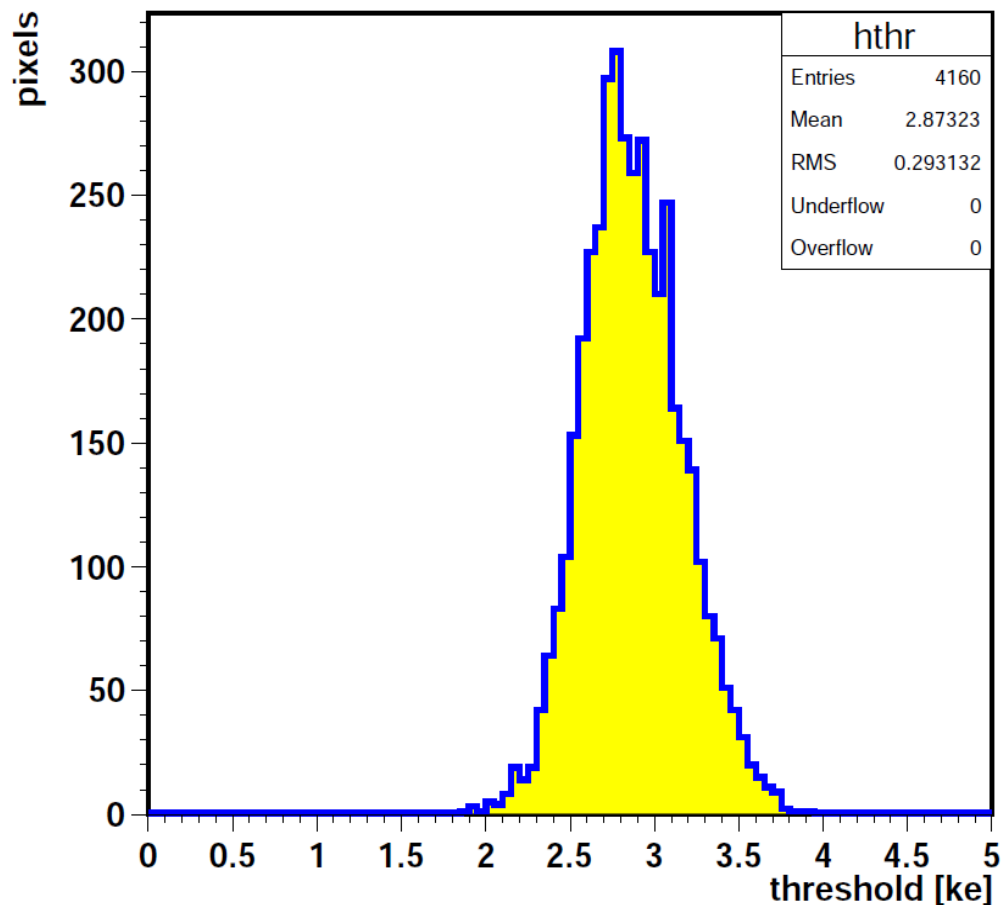


threshold broadened by noise
fit by error function
noise: 130 e



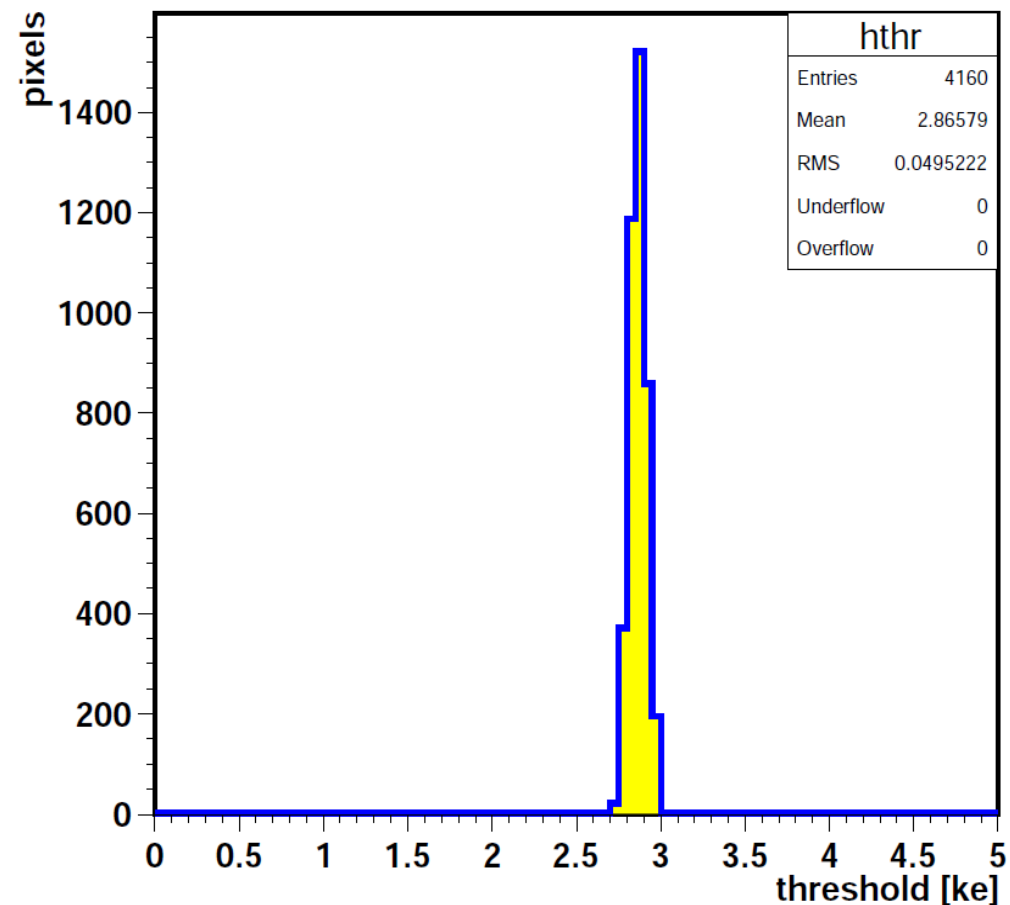
Threshold variation

4160 pixels / cip



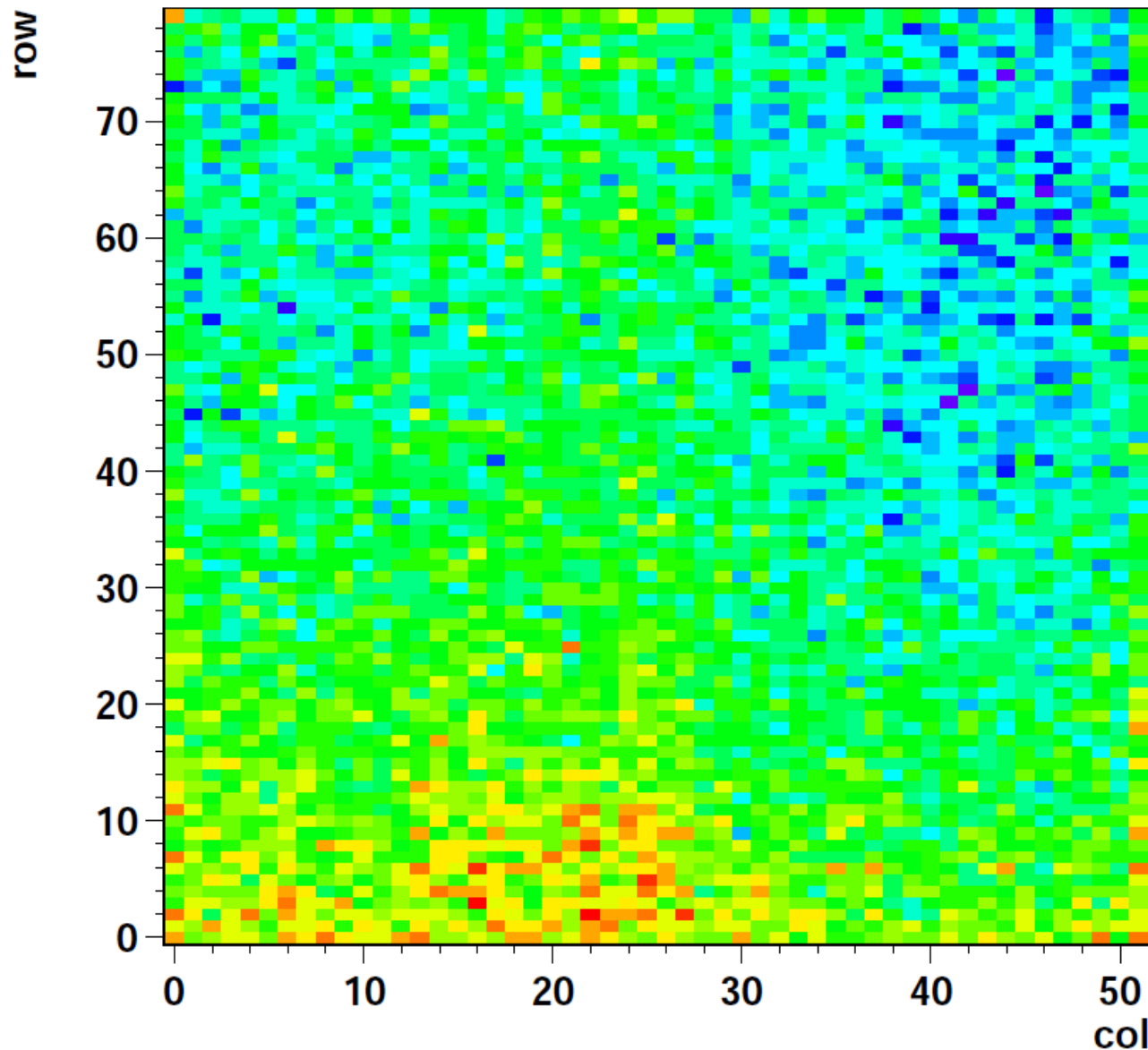
**CMS transistor variations:
threshold spread 290 e**

the same chip, trimmed:



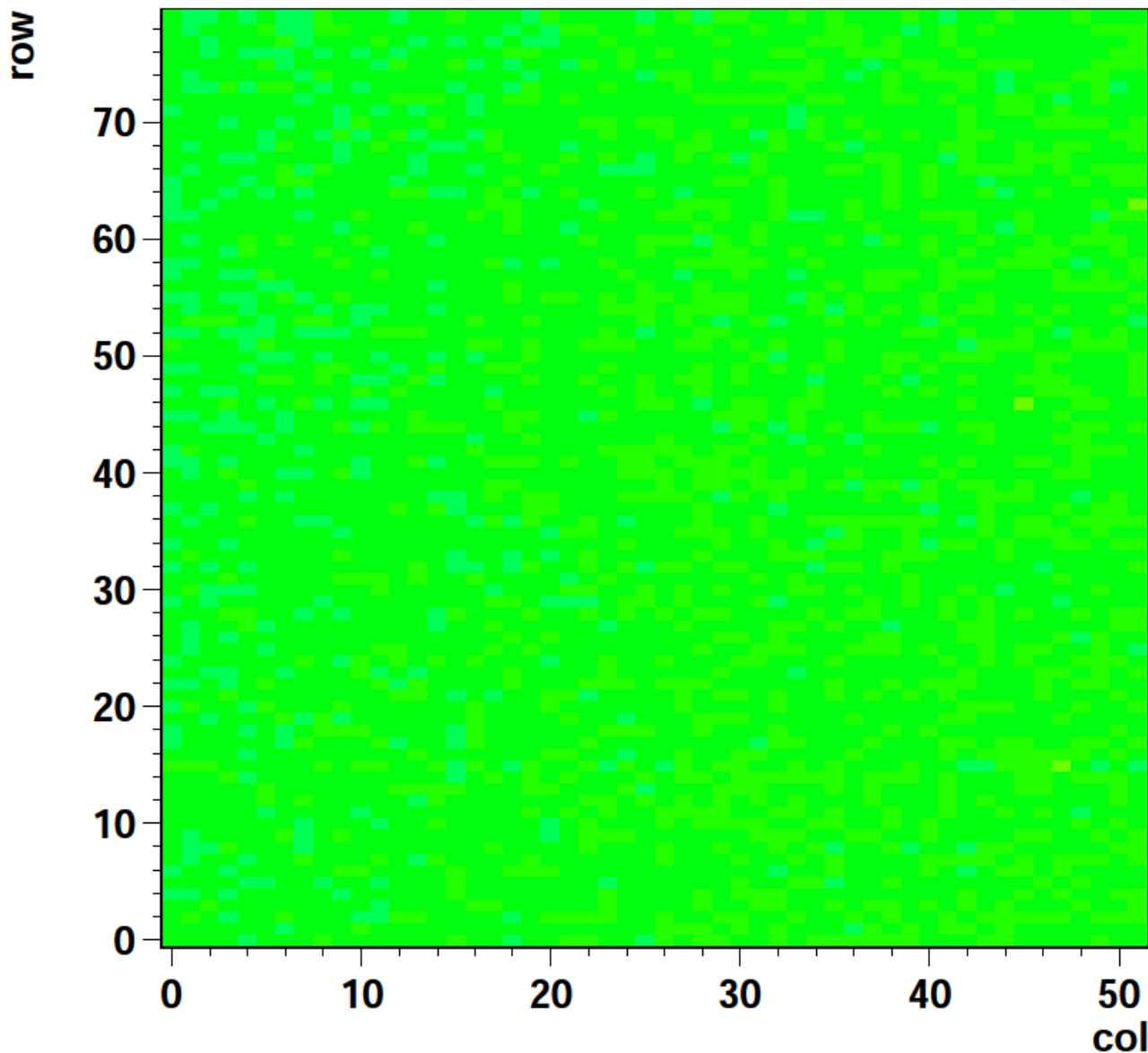
**4-bit DAC trimming:
threshold spread 50 e**

Threshold variation untrimmed



- Vertical scale - threshold in ke
- Chip 0 (no sensor)
- VthrComp 124
- 10% spread

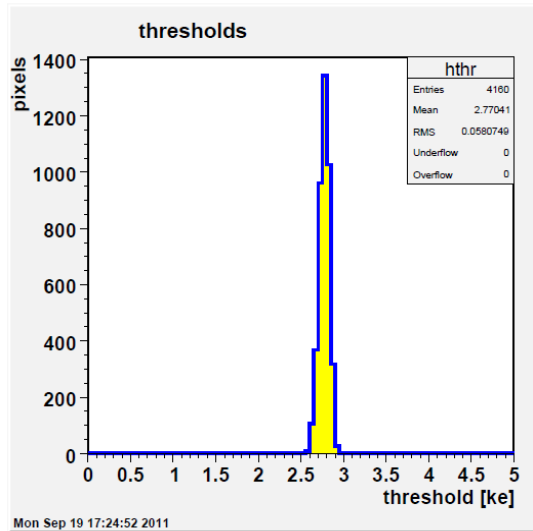
Threshold variation trimmed



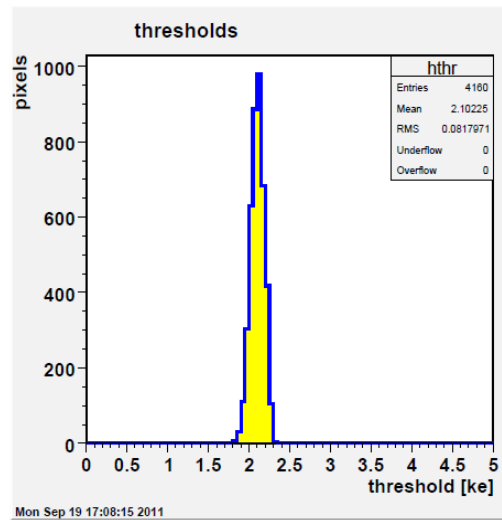
- Chip 0 (no sensor)
- VthrComp 112
- Vtrim 104
- 4160 TrimBits set.
- time: 3 min / chip
- 1.7% spread
- 50 e threshold variation!

Towards the minimum TrimVcal

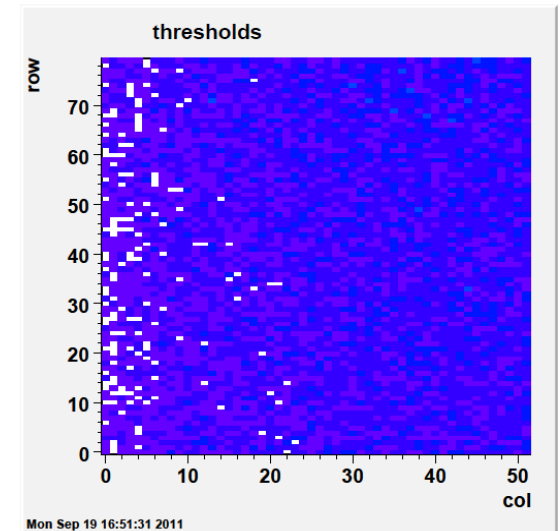
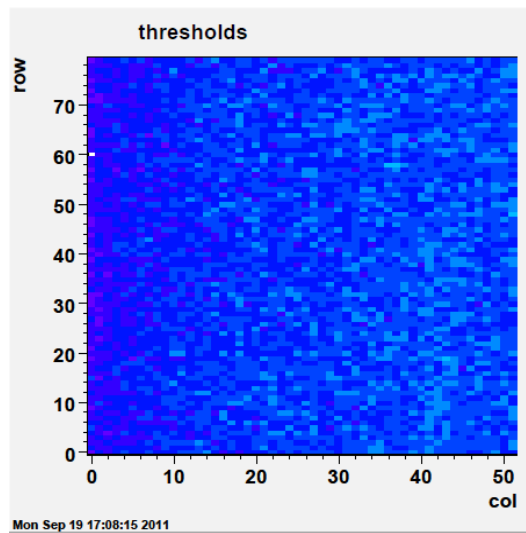
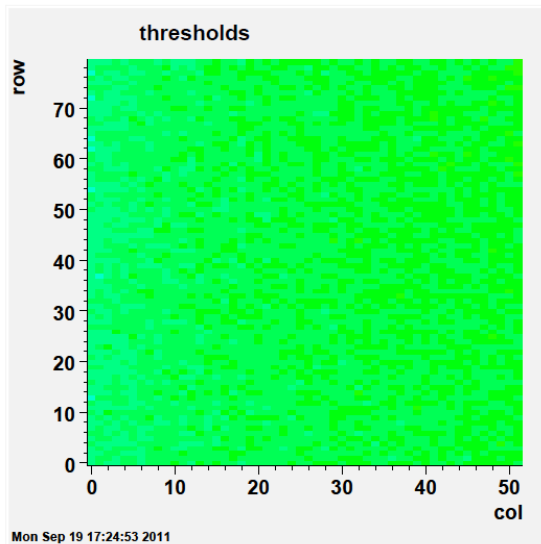
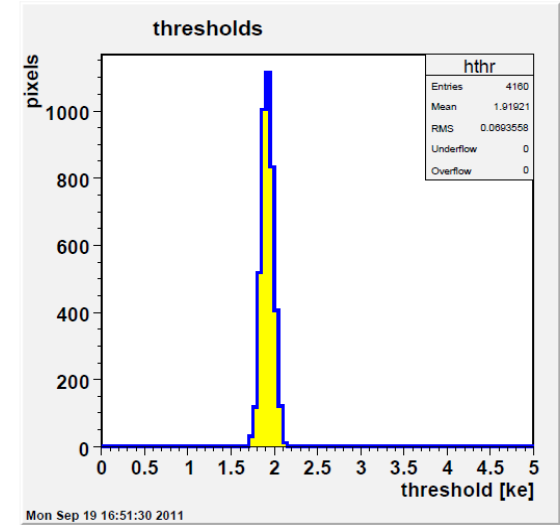
TrimVcal=40



TrimVcal=32



TrimVcal=28

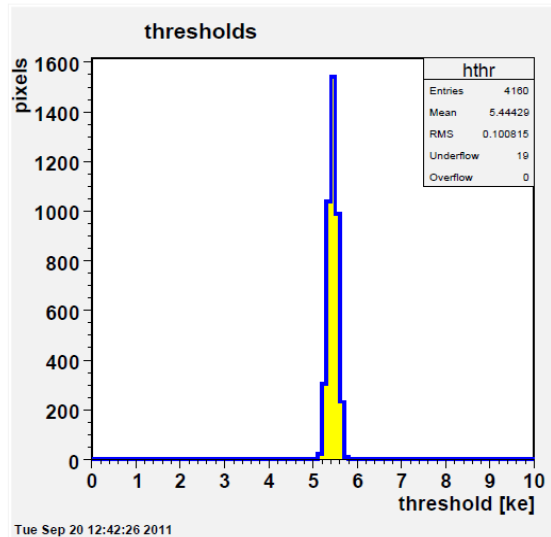


Use as low as possible target Vcal: good charge sharing, good for radiated chip with low charges.

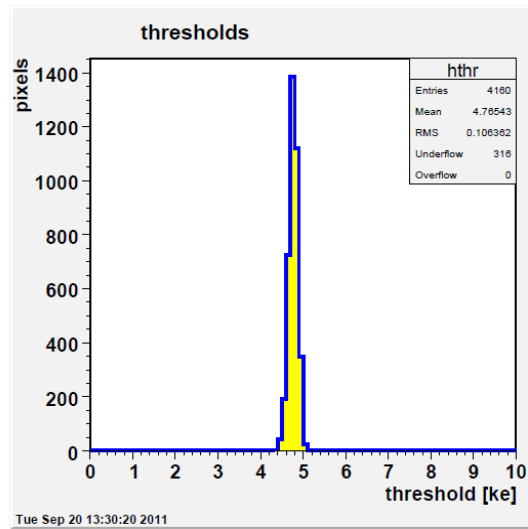
Chip2 (no sensor)

Tests with sensor

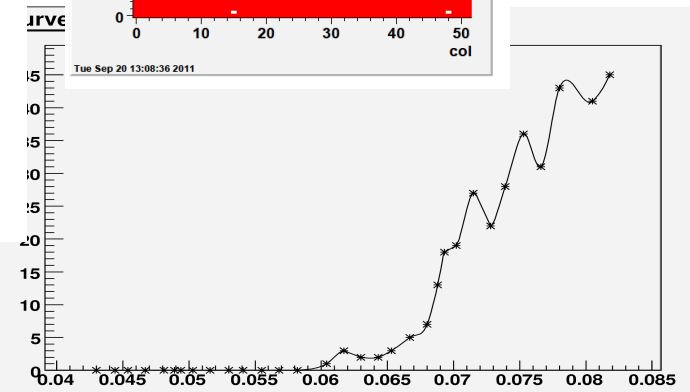
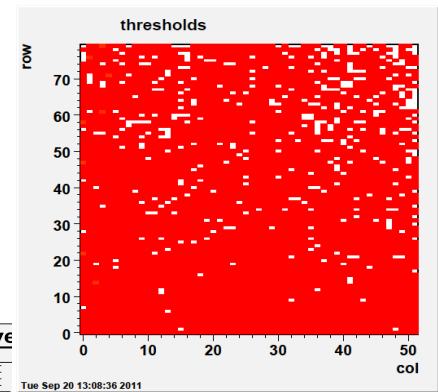
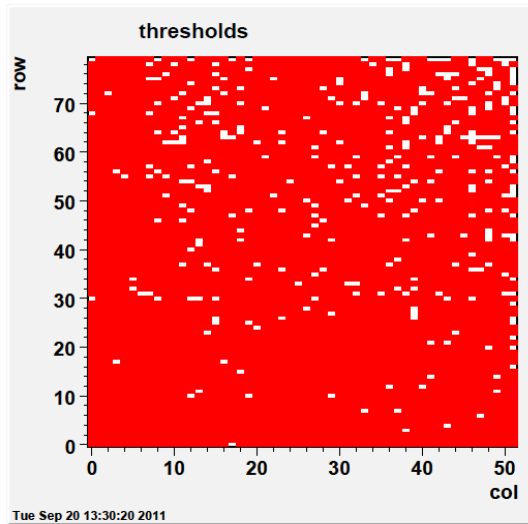
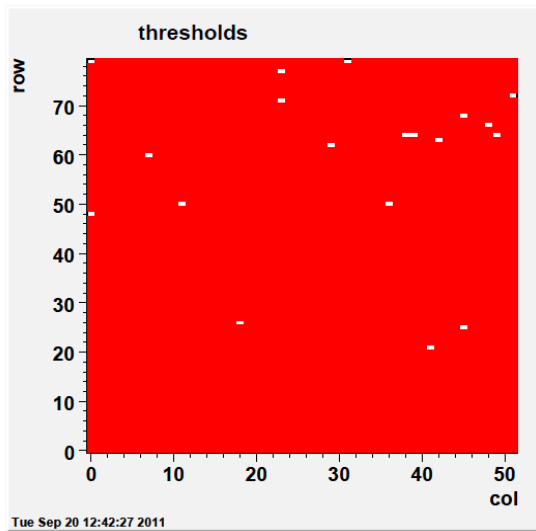
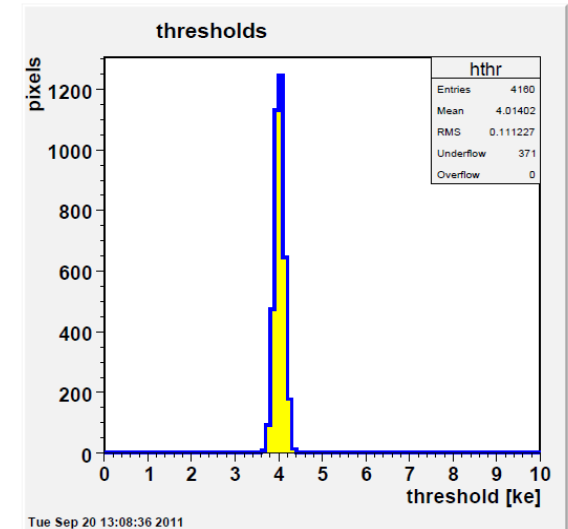
TrimVcal=80



TrimVcal=70



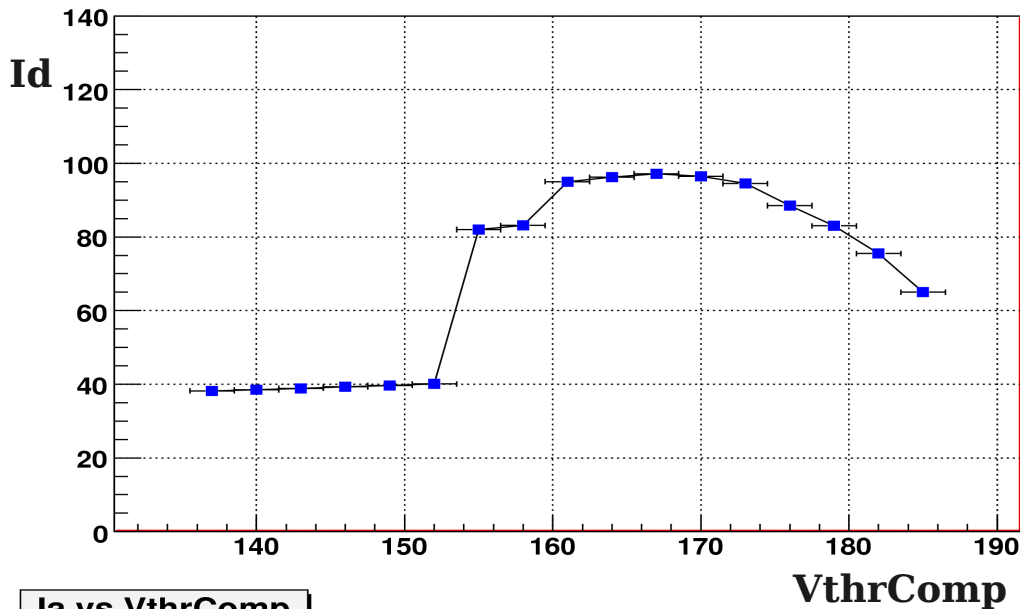
TrimVcal=60



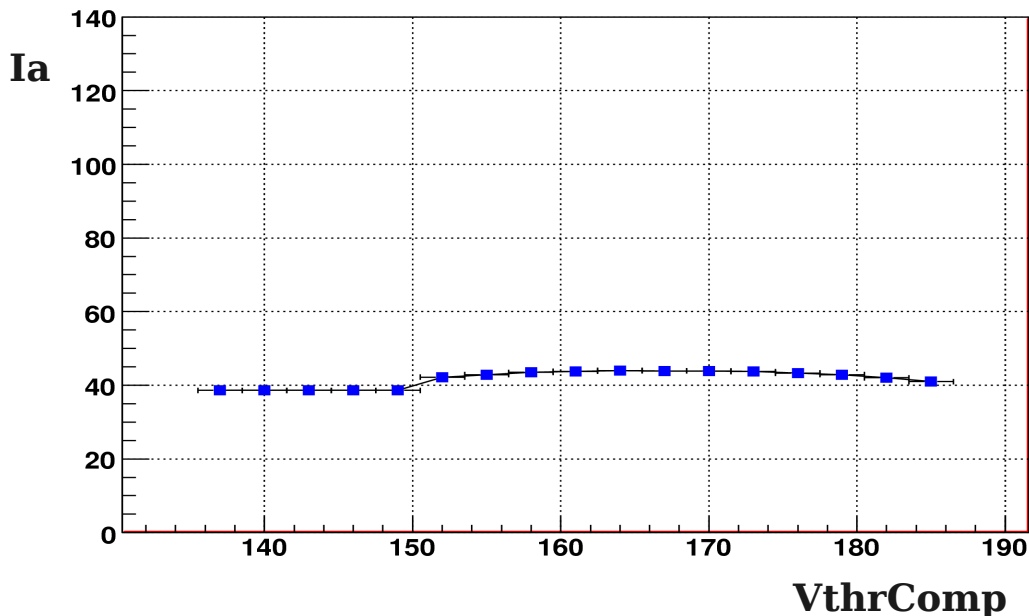
Underflows: bad fit of SCurves
Chip6 (with sensor)

Threshold Scan and Power

Id vs VthrComp

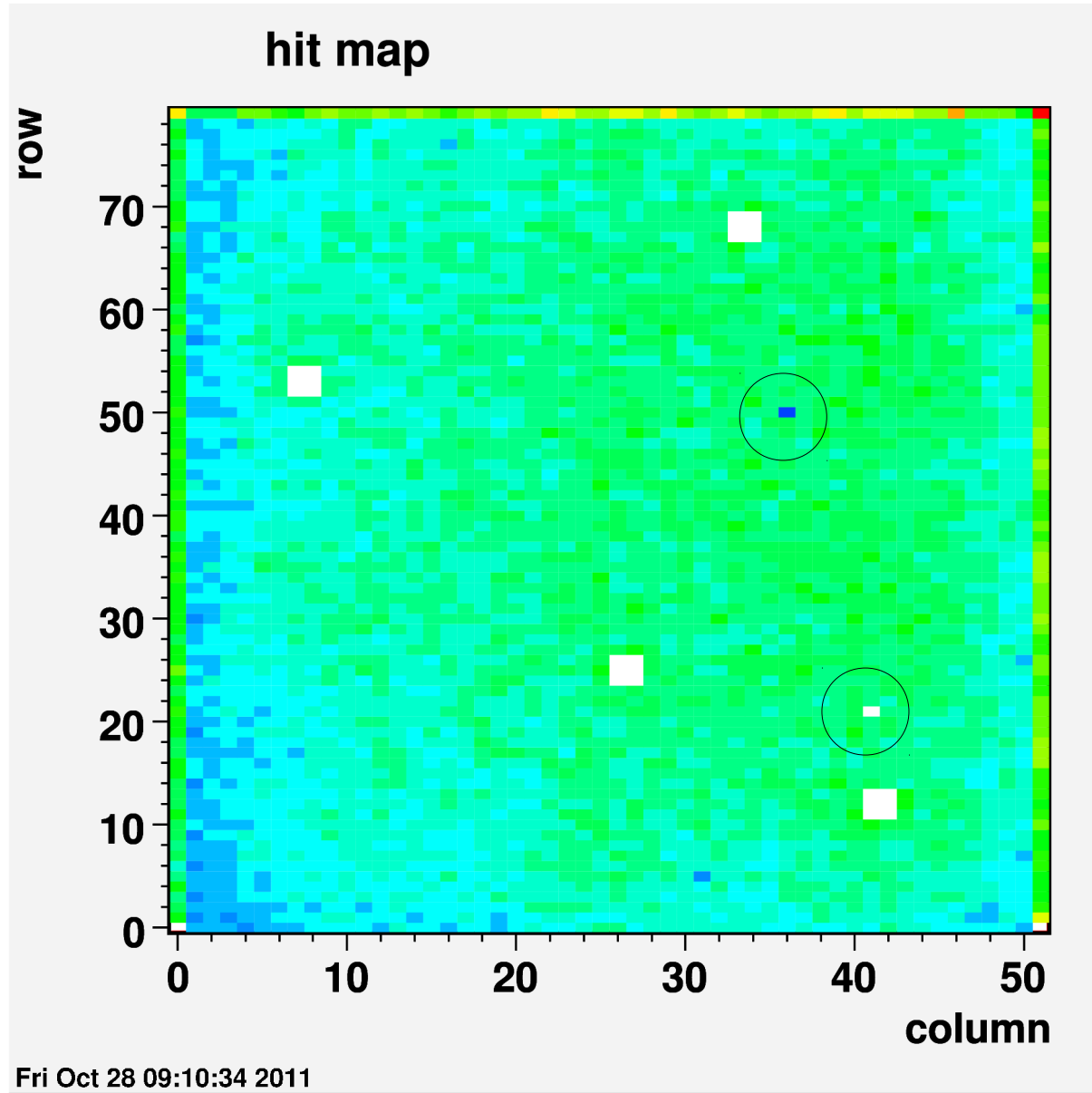


Ia vs VthrComp



- Chip 2 (no sensor)
- Id (mA) vs VthrComp
- Threshold into noise
- Chip consumes 2.5 times more power at low threshold (high VthrComp)
- Chip 2 (no sensor)
- Ia (mA) vs VthrComp
- Small effect at low threshold
- The same trend for Chip 6 (sensor)

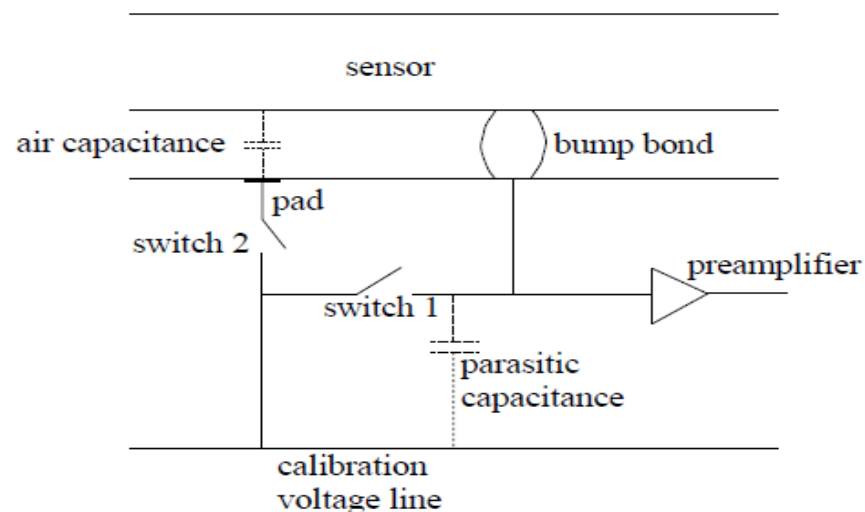
Test beam hit map



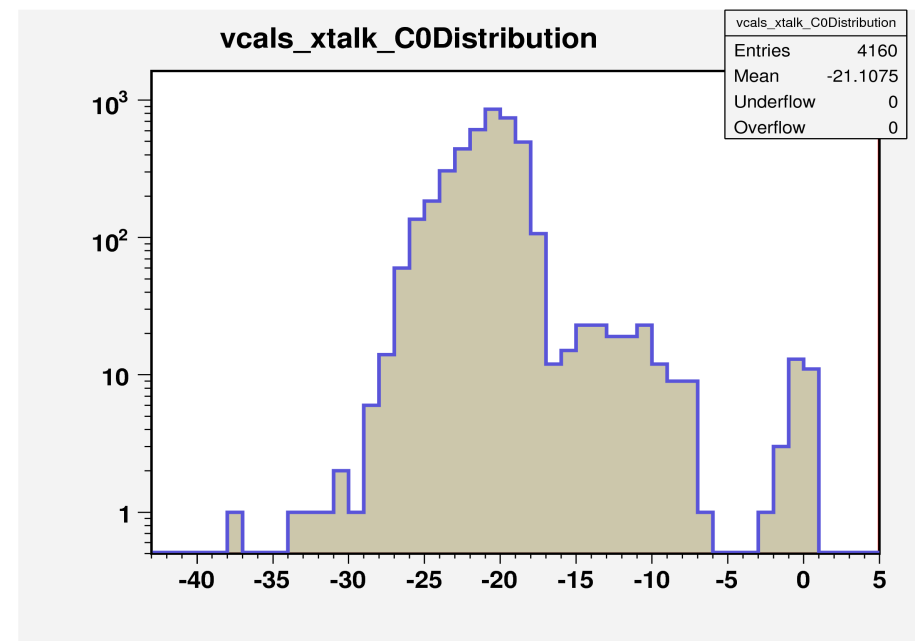
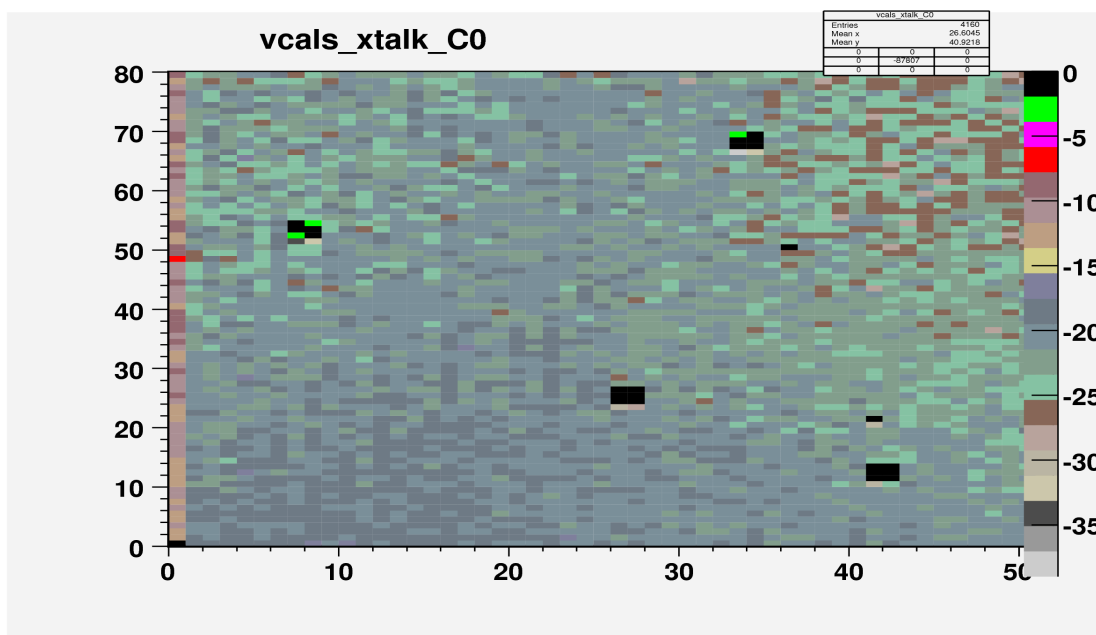
- 2 GeV e^+ test beam
- Chip 6 (sensor)
- 2 dead pixels
- 4 dead regions
- Use 'psi46expert' to test bump bonding

Bump Bonding Test Procedure

- Vcal to switch 2 induces a signal in sensor. If bump bond (bb) is present it is seen by preamplifier: missing bb can be identified
- Problem: cross-talk via a parasitic coupling between the calibration voltage line and preamplifier can fake a signal even without bb
- Determine Vcal_Thr2 for the signal injection through the sensor
- Measure Vcal_Thr1 for the parasitic cross-talk (with both switches open)
- $|V_{cal_Thr1} - V_{cal_Thr2}| < 5 \text{ DAC units} \rightarrow \text{defect bump bonding}$



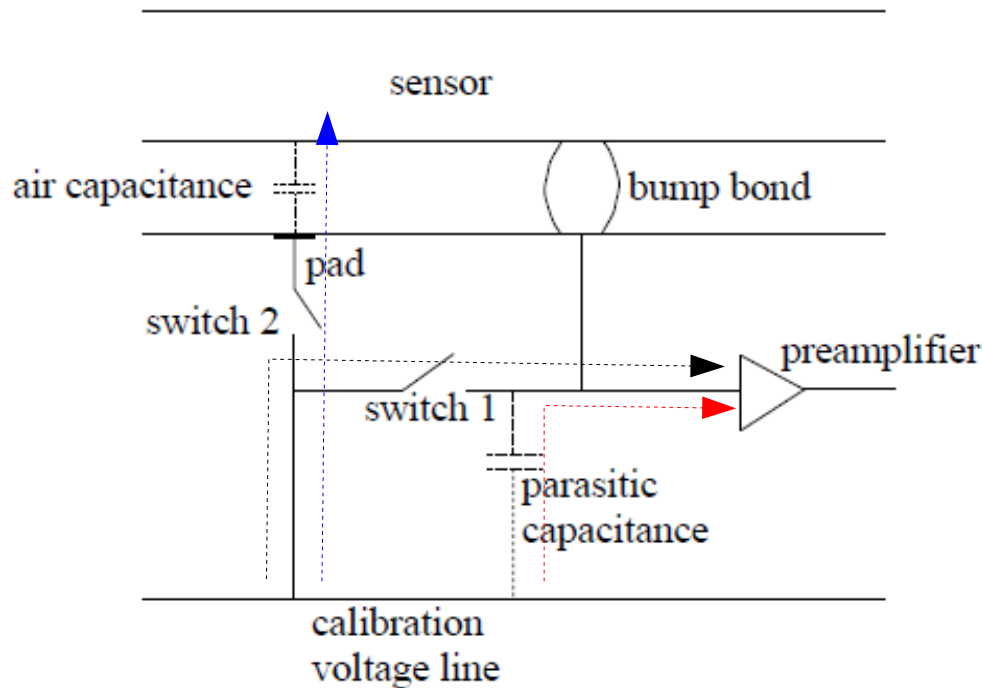
Bump Bonding Test Results



Δ Threshold

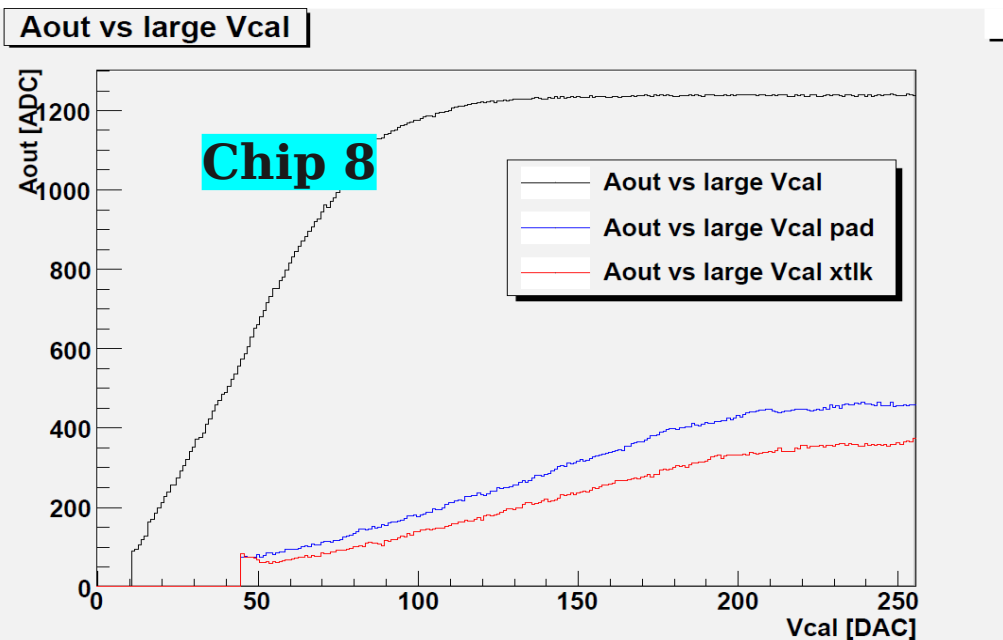
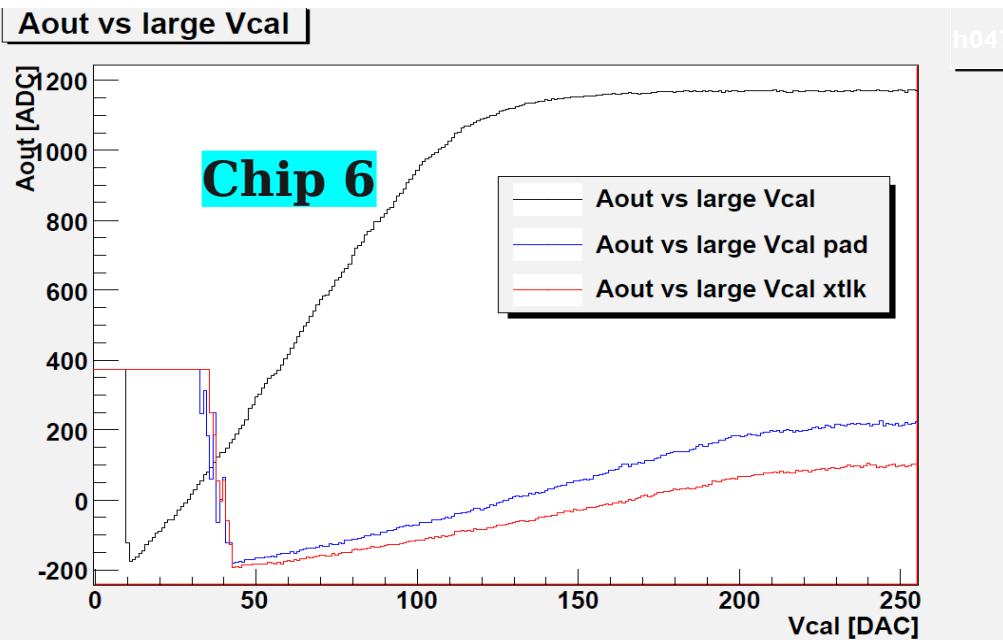
- Threshold difference: expected defects from beam test are correctly identified by 'psi46expert'
- Peak at Δ Threshold $\sim -20 \rightarrow$ good bump bonds. Peak at Δ Threshold $\sim 0 \rightarrow$ bad bump bonds

Arm Pad, Xtalk



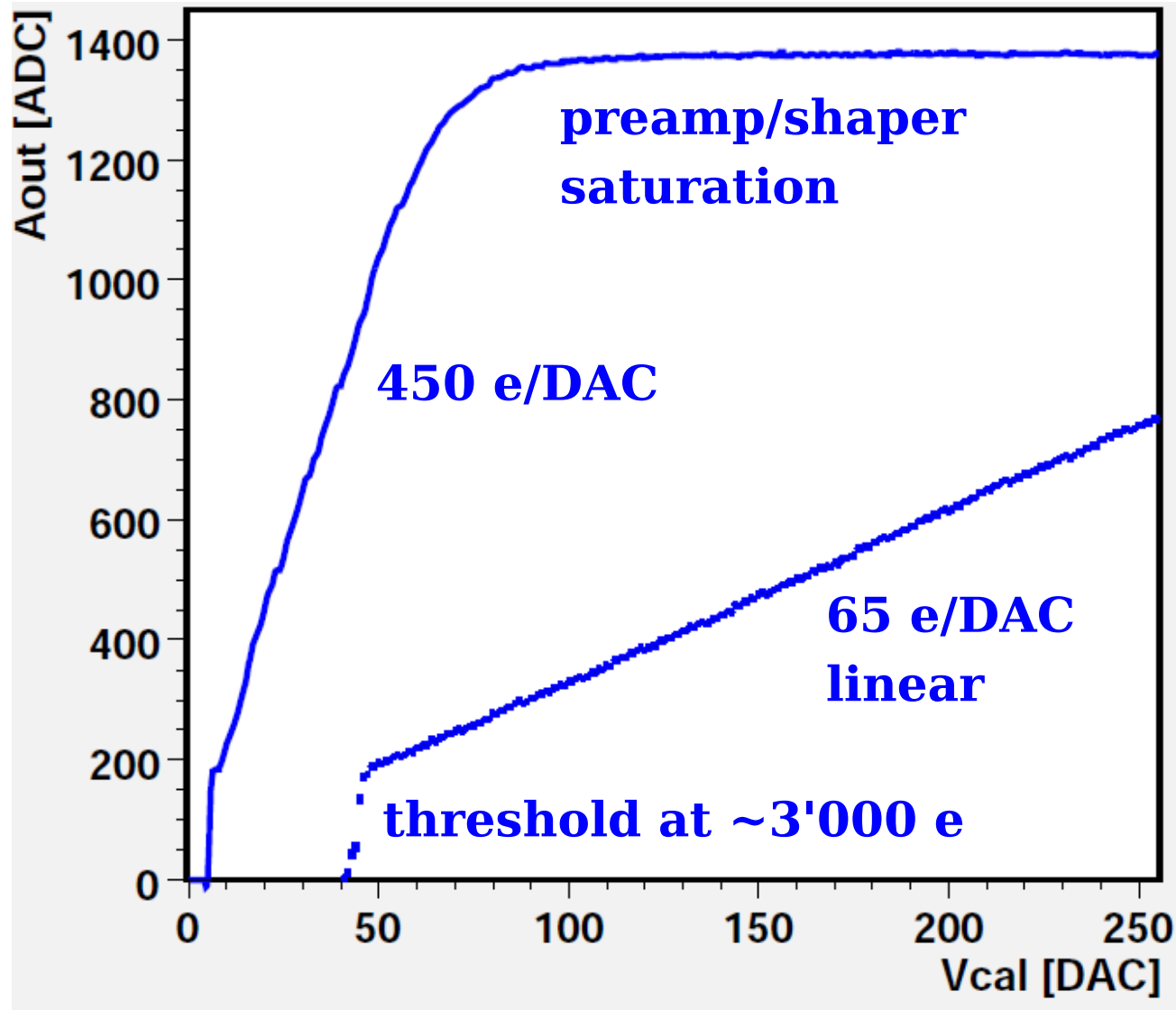
- Three ways to inject charge: Standard (used so far), via '[pad](#)' and through '[Xtalk](#)'
- Different signals can be used for bump bonding test of modules, cross calibration of ROCs and some other purposes ?

Arm Results



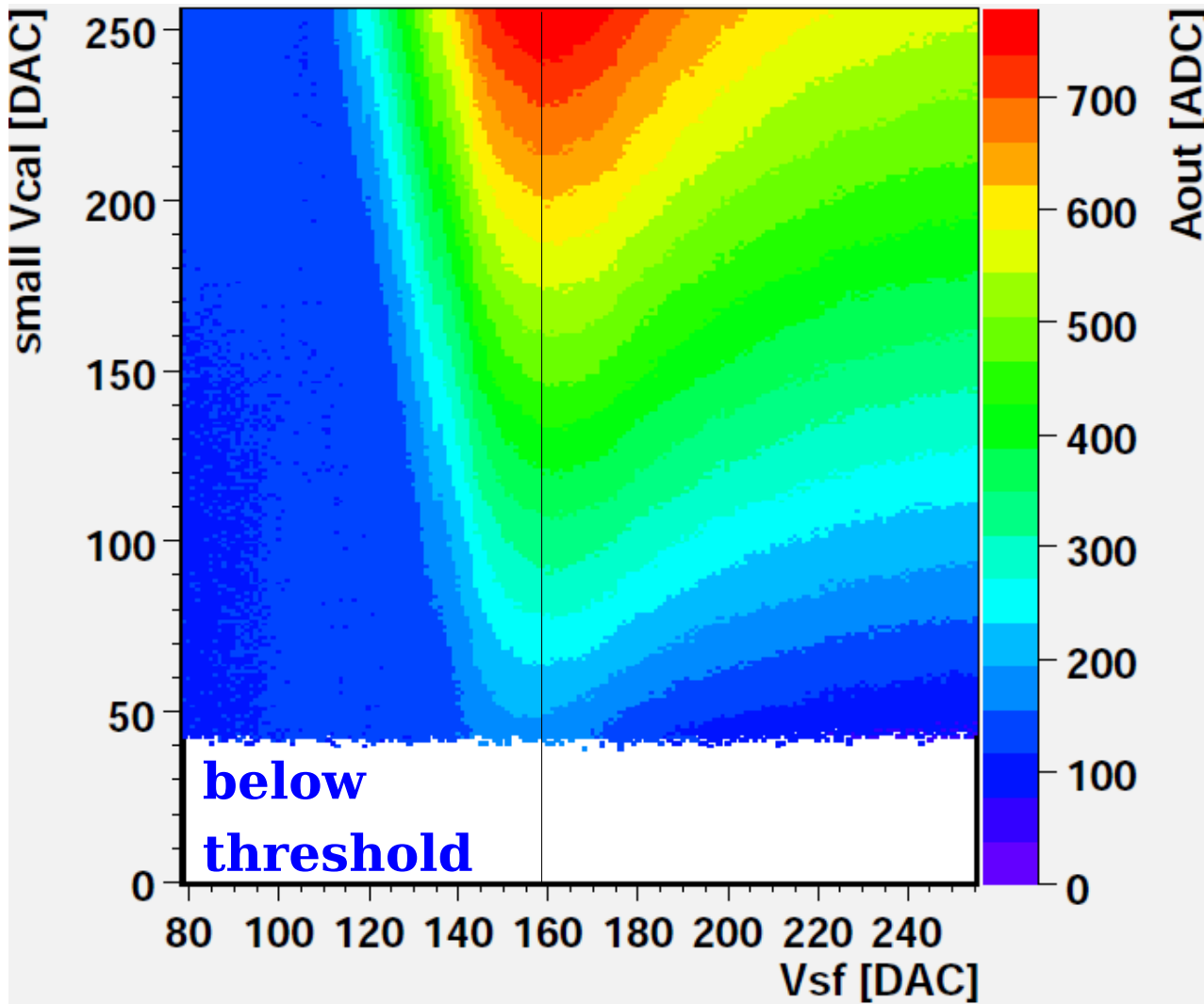
- Use three different capacitances to inject charge: **direct**, **via sensor**, and **crosstalk**:
 - $Q = C_x \cdot V_{cal}$
- One pixel activated.
- Draw PH [ADC] vs calibrate amplitude for large Vcal (450 e/DAC)
- Use sensor type ROCs
- Chips 6, 8 show similar behaviour but PHs are different (different config. parameters for analog gain and offset)
- Blue and Red curves start to saturate later compare to black - ?

gain and linear range

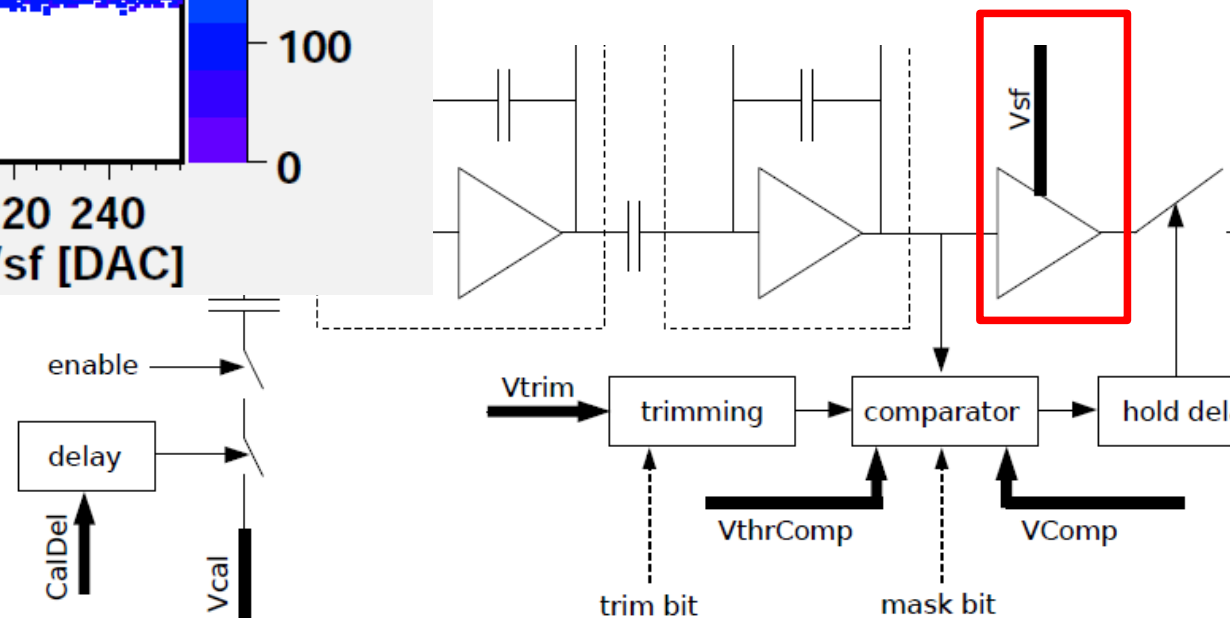


- One pixel.
- 2 Vcal ranges (PSI X-ray calibration):
 - CtrlReg 0 or 4,
 - 65 ± 5 e/DAC,
 - 450 e/DAC.
- Linearity for small pulses important for spatial resolution using charge sharing.
- Saturation around 36'000 e (~ 1.6 MIP).

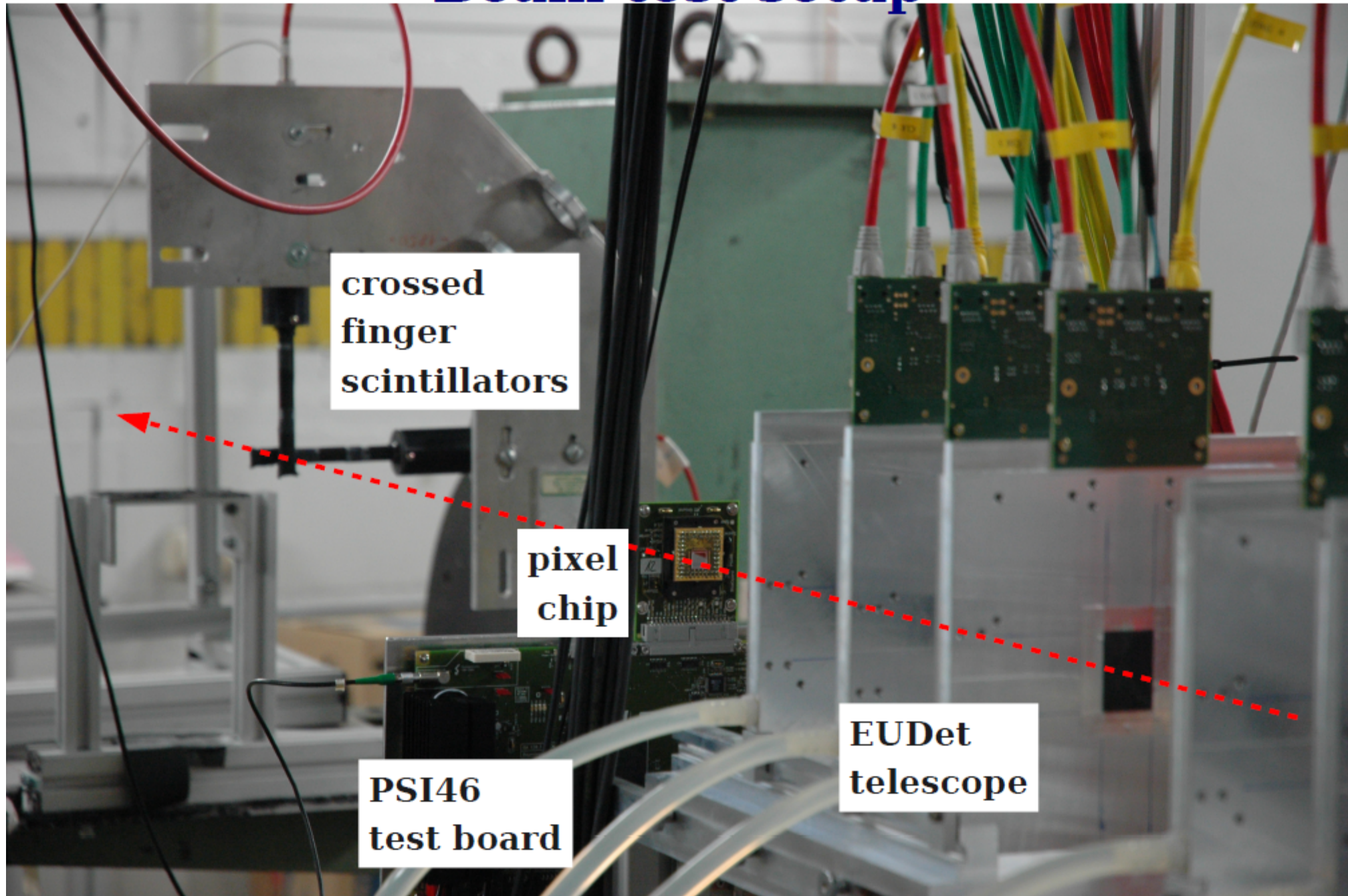
Linear range vs Vs_f



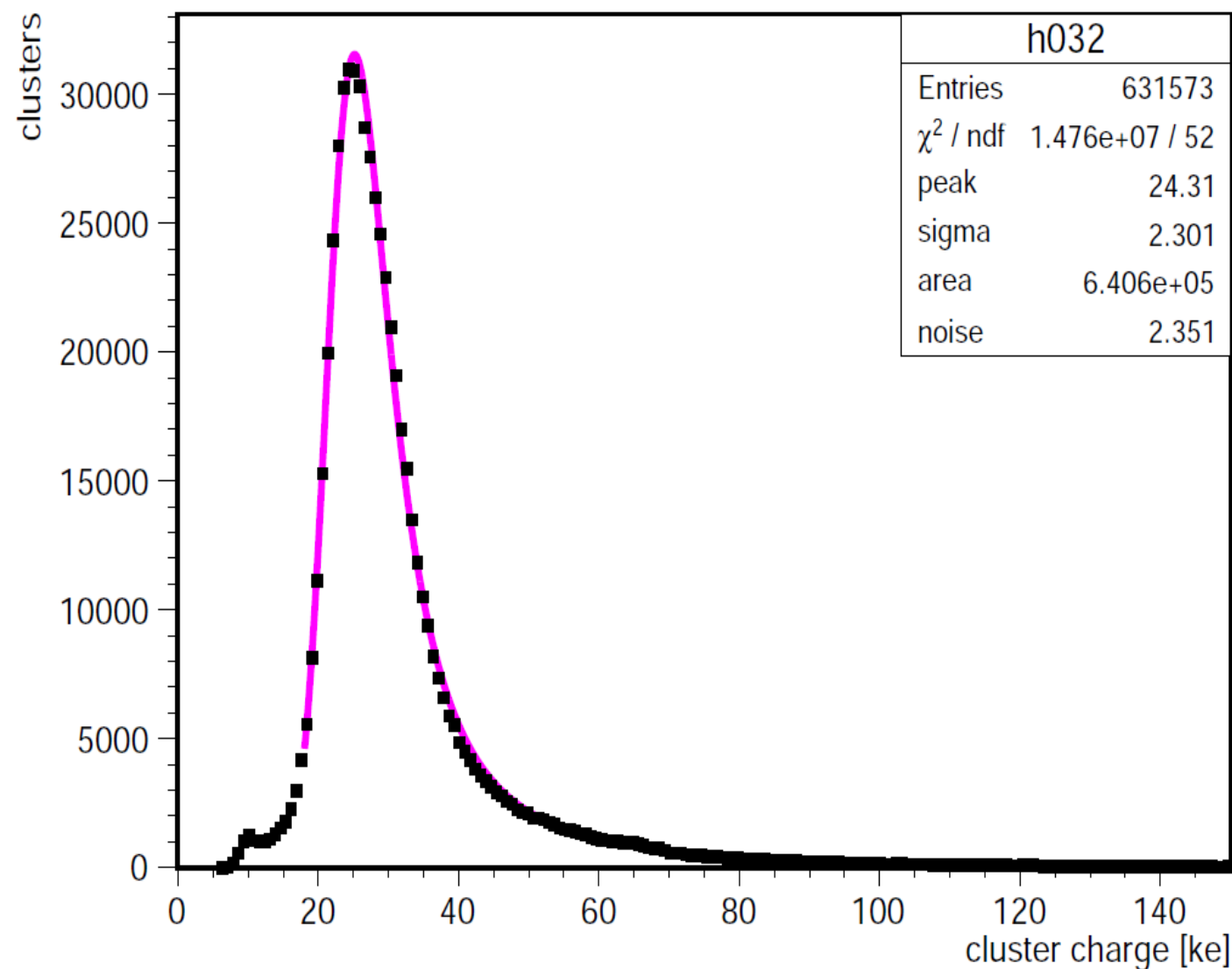
- One pixel
- Analog pulse height vs calibrate amplitude and source follower voltage.
- Best linearity in valley.



Beam test setup



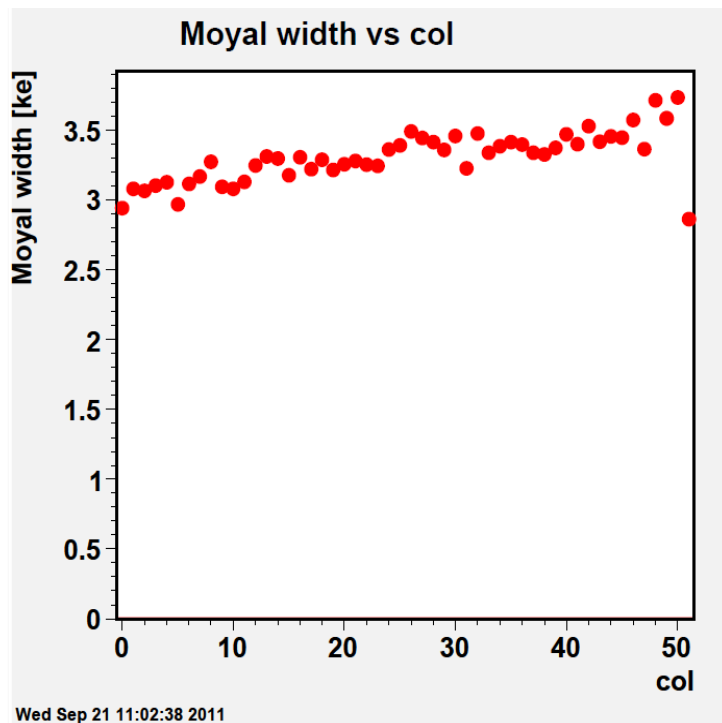
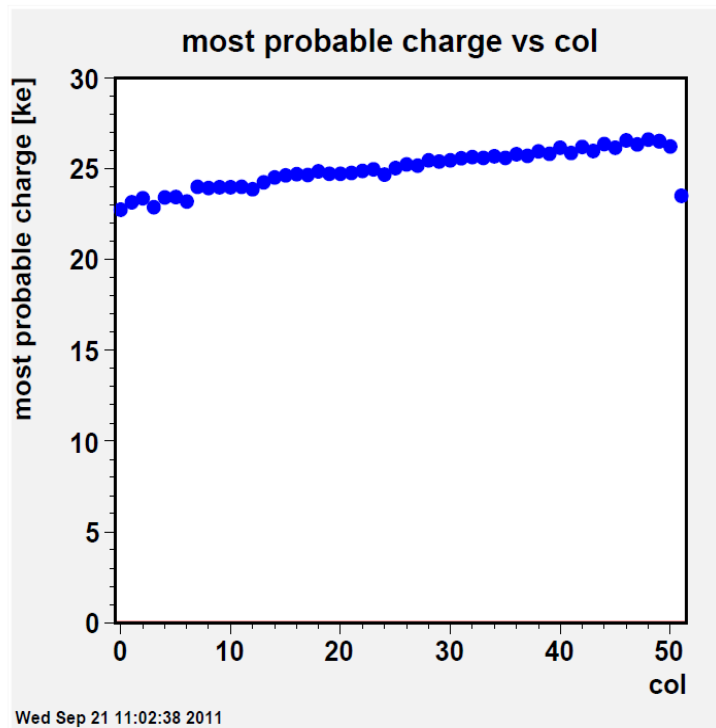
Pixel detector in DESY test beam



- 2 GeV e^+ beam.
- Landau \otimes Gauss:
 - Fit not perfect:
 - Peak position and width OK for 285 μm silicon,
 - noise too large.
- Small peak at small pulse height:
 - Wrong timing due to missing synchronization between clock and beam.

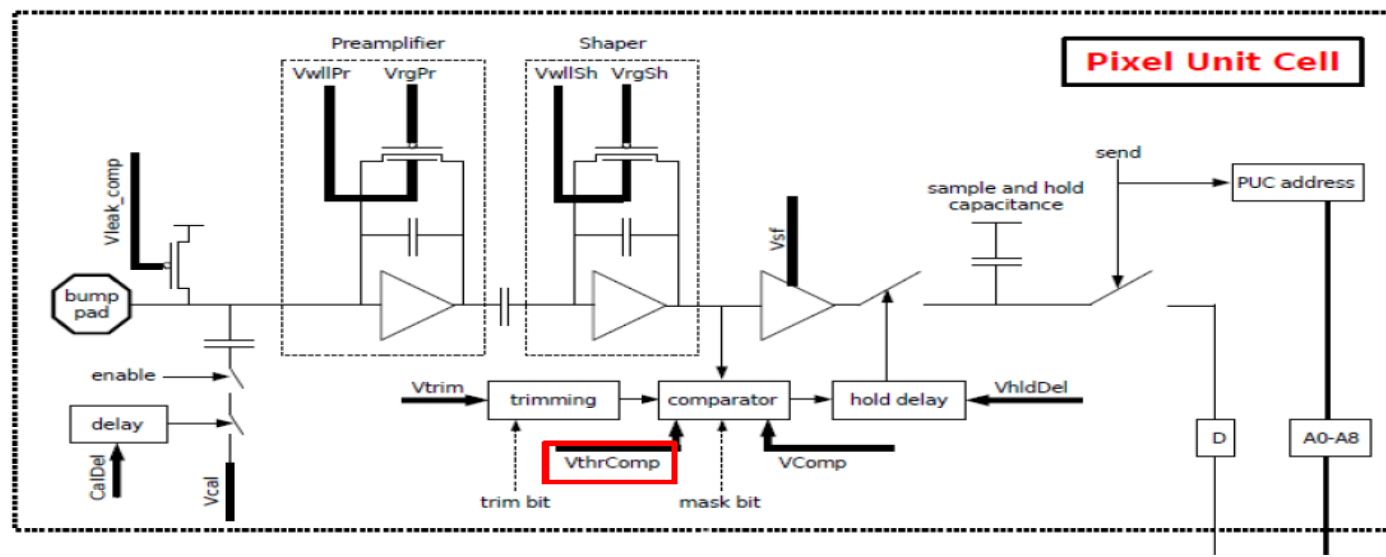
Cluster charge

- 2 GeV e+ beam test
- No magnetic field
- Test pulse gain calibration applied
- Chip 8, all pixels
- Moyal fit to each column
- Expect ~ 25 ke from $285\text{ }\mu\text{m}$ silicon
- Observe $\sim 8\%$ gain variation across chip8:
 - Test pulse (calibration) problem?
 - Check with X-ray source?



Threshold Scan Procedure

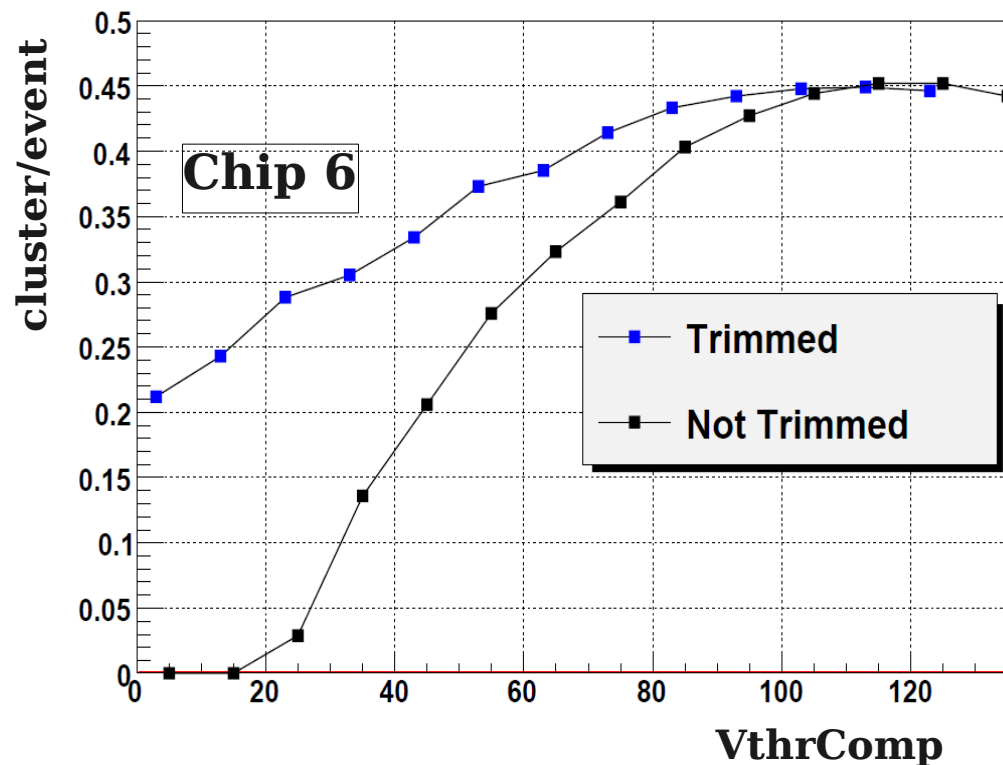
- DESY 2 test beam: 2 GeV e+, 5 kHz scintillator trigger, Vbias -90 V
- Chips 6, 8 (sensor), calibrated, trimmed, optimal DAC parameters
- 50 sec runs, 0 - 140 k clusters per run
- Change VthrComp from lowest to optimal DAC units. Large DAC = soft threshold



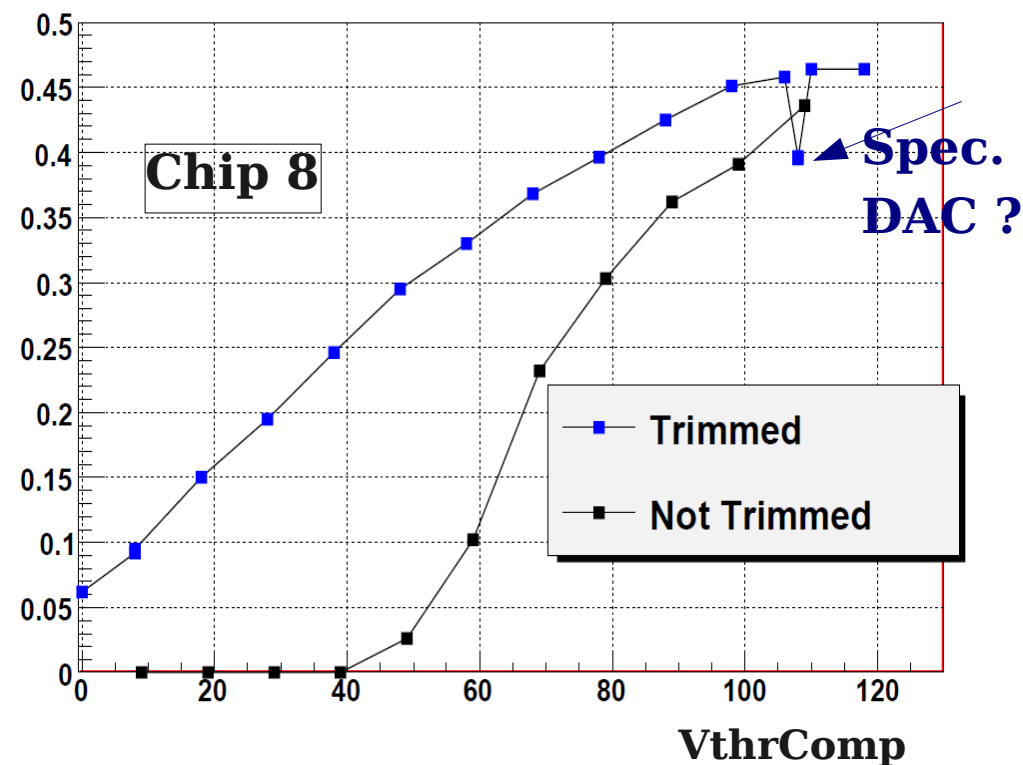
— adjustable by programmable DAC, per ROC

Threshold scan in the test beam

clusters/event vs VthrComp for Chip6



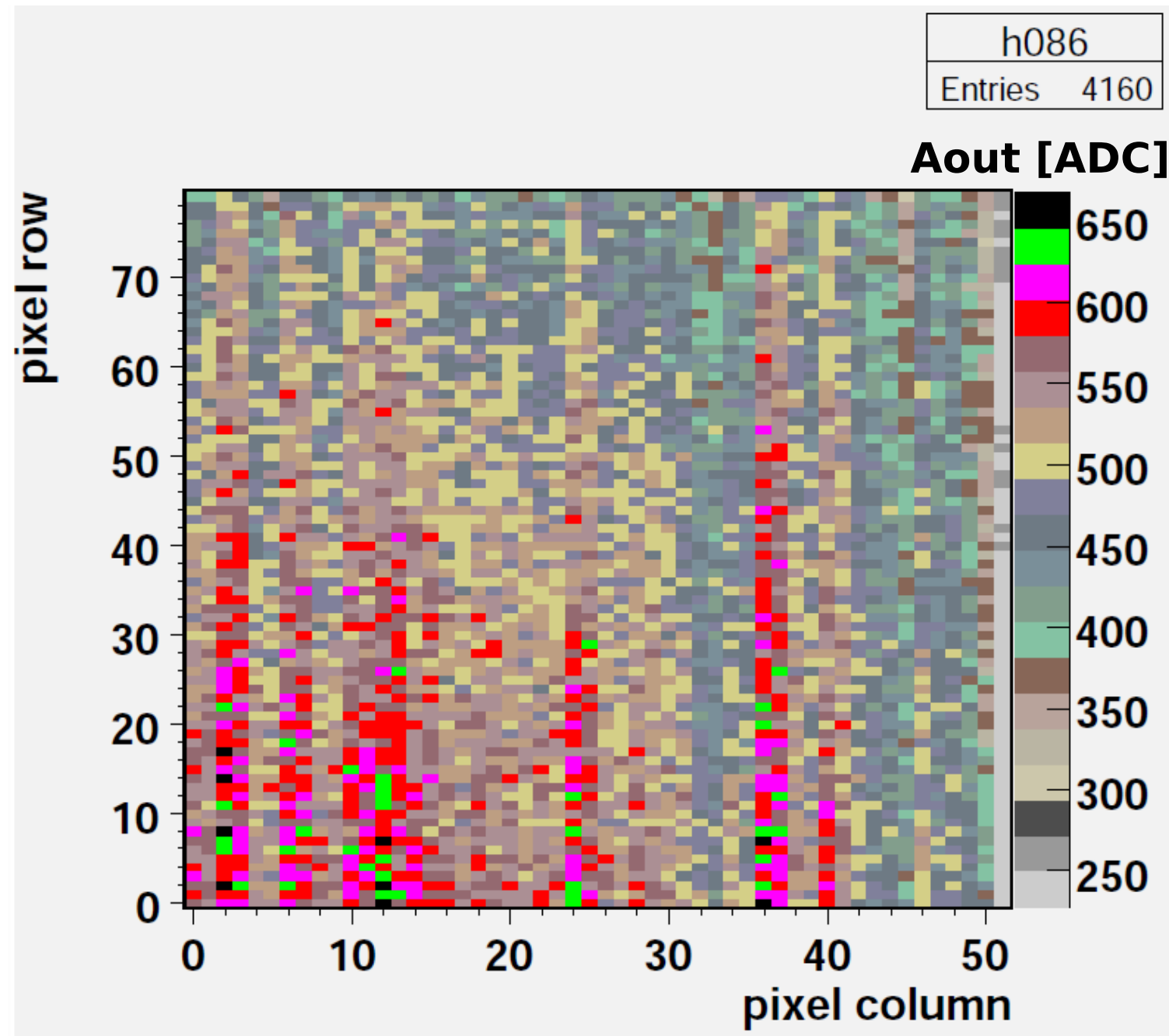
clusters/event vs VthrComp for Chip8



- Uniforming of thresholds brings more clusters per event
- Different chips show closer behaviour after the trimming procedure
- Special DAC value found for Chip 8?

Known issues

Pixel map



- $52 \times 80 = 4160$ pixel per chip.
- $V_{cal} = 200$ DAC
- $V_{thrComp} = 80$
- Strong pulse height variation:
 - gain?
 - timing?

Open questions

- Many optimization procedures use fast reading of FPGA data (scurve data) but it works in TBM emulator mode only
- We can not see UB level in TBM emulator mode. Firmware Version ATB V6.1 (27.08.2010 15:35) ID=22A71BED TS=4C84D636.

Done so far:

- ▶ 3d scans: clk (LHC clock), sda (DACs programming), rda (token out signal). Takes 2 hours each, ~2 days in total → no UB level
- ▶ TBM DAC 'Dacgain' (UB TBM) and 'Ibias_DAC' (UB ROC to UB TBM) have no effect to UB level

- ▶ No TBM:

Data: 6 : -211 17 126 : -45 15 190 73 -44 189 : 7 8 7 8 7 9

- ▶ TBM (gain 4, longer header and trailer):

Data: -750 -750 -750 0 374 374 186 : 374 68 500 : -172 64 752 292 -176 764 : 32 -750 -750 0 0 374 -188 186 -188

- We need to use bigger time delays between FPGA and USB before data transfer to PC. Fast computers, slow USB-1 ? Example:
 - ▶ Data lost at beam test: slow USB, time window was not wide enough for sending of large data blocks. Solved by reducing of data block size sent via USB from 2^{15} to 10.000

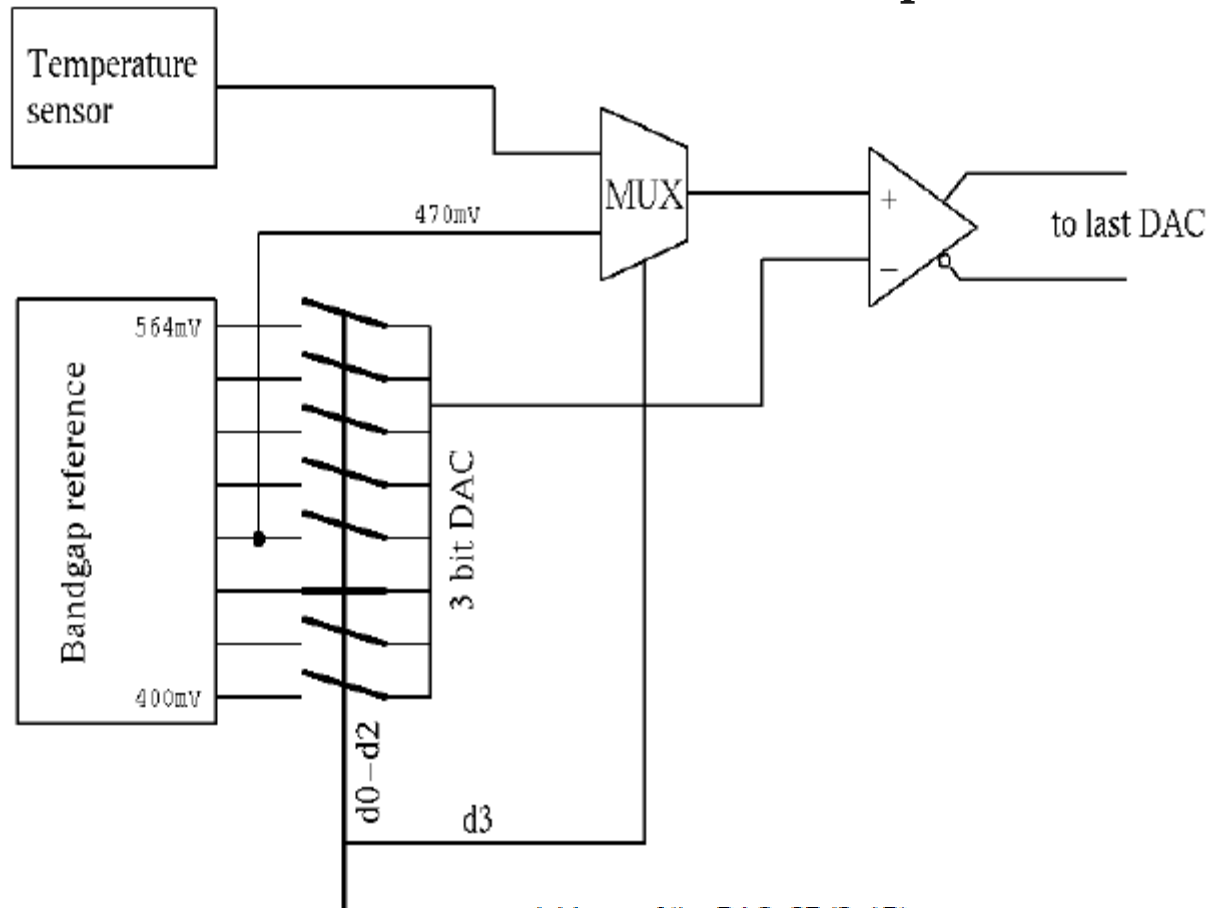
Back up slides

Temperature test [Temp]

- The CMS pixel readout chip has a built in temperature sensor designed to measure temperatures in the range $[-30^{\circ}\text{C}, +70^{\circ}\text{C}]$
- Test signal is a LastDac ADC signal (LD) \sim to voltage difference between T sensor (temperature dependent) and reference (temperature independent)
- For better accuracy 8 different windows (reference voltages 400 – 564 mV) of measurement are defined: one part of T° measurements compared to one V window, another part to another V window etc. Windows are programmed by register 27 'RangeTemp'
- Calibrate output signal to extract the voltage difference from the measured LD ADC value. The sensor output signal is replaced by 470 mV for calibration. Make a linear fit to the calibration points differ from the ROC Black level. This fit is used to determine the measured voltage difference, which is finally added to the known reference V to get a sensor voltage

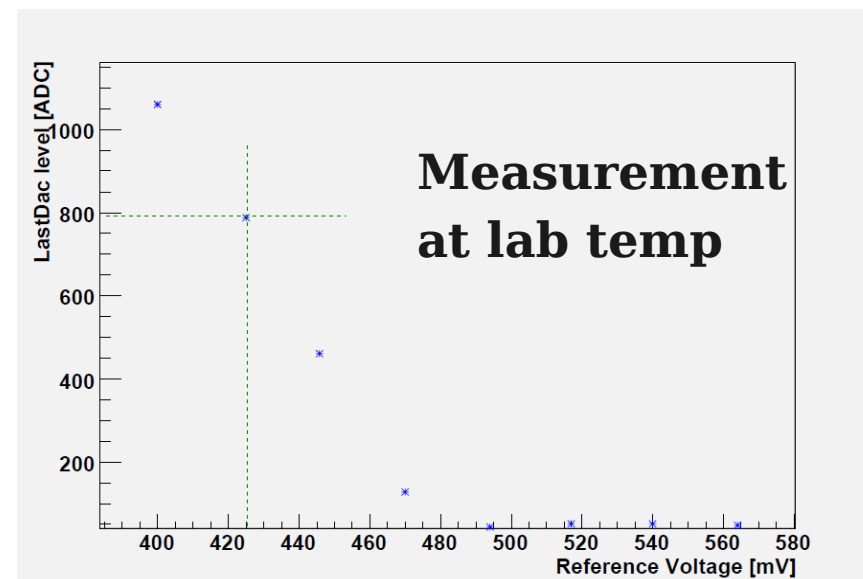
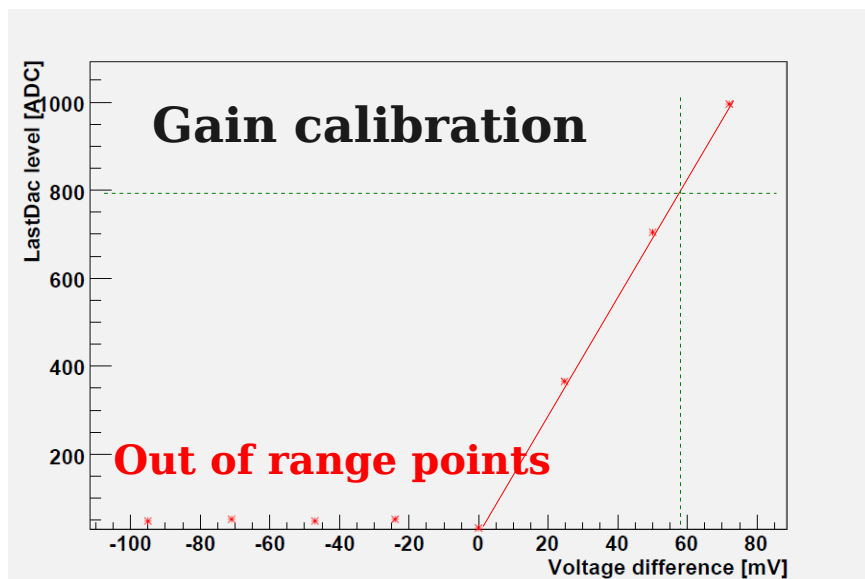
T measurements

PSI46 Specification:



- Address of the DAC: 27 (0x1B)
- The first 3 data bits set the reference voltage in the range [399.5mV, 564mV] in steps of 23.5mV (unirradiated).
- Bit 4 switches between the temperature sensor output voltage (bit cleared) and a fixed voltage of 470mV (bit set).

Temperature test results



Voltage difference = $V_{ref} - 470 \text{ mV}$

- Example chip 2:
 - Look at ref. Voltage = 425 mV
 - measure LD = 800 ADC,
 - $\Rightarrow V \text{ difference} = 58 \text{ mV}$
 - Sensor $V_{temp} = 425 + 58 = 483 \text{ mV}$
 - $T = 0.625 (V_{temp} - V_{mid})$

Average temperature (°C) measured by different ROCs

Chip 0	Chip 1	Chip 2	Chip 3	Chip 4	Chip 5	Chip 6	Chip 7	Chip 8
17	16	21	19	17	21	20	17	16

Temperature may increase by 3°C during test